

Performance of novel VUV-sensitive Silicon Photo-Multipliers for nEXO

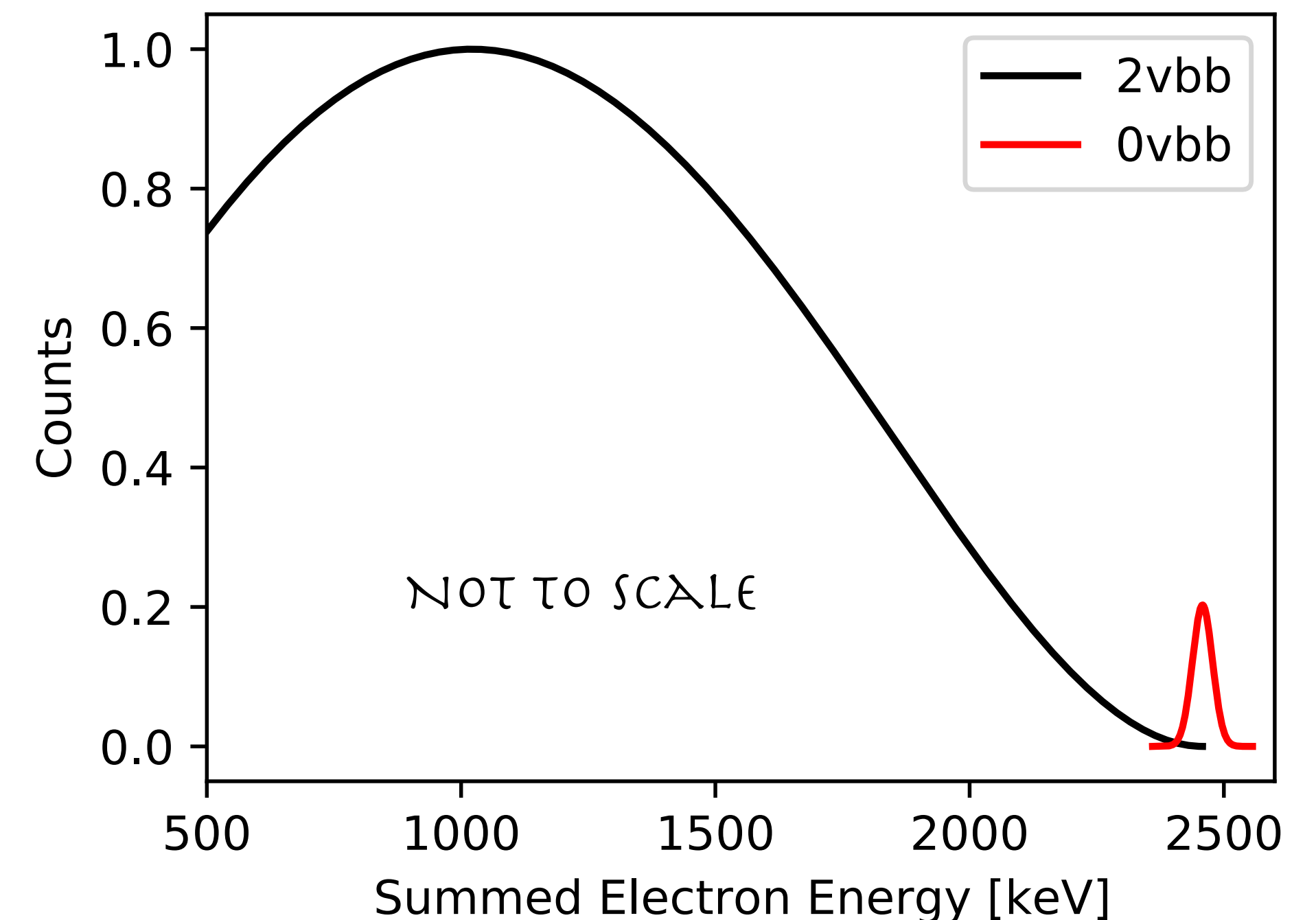
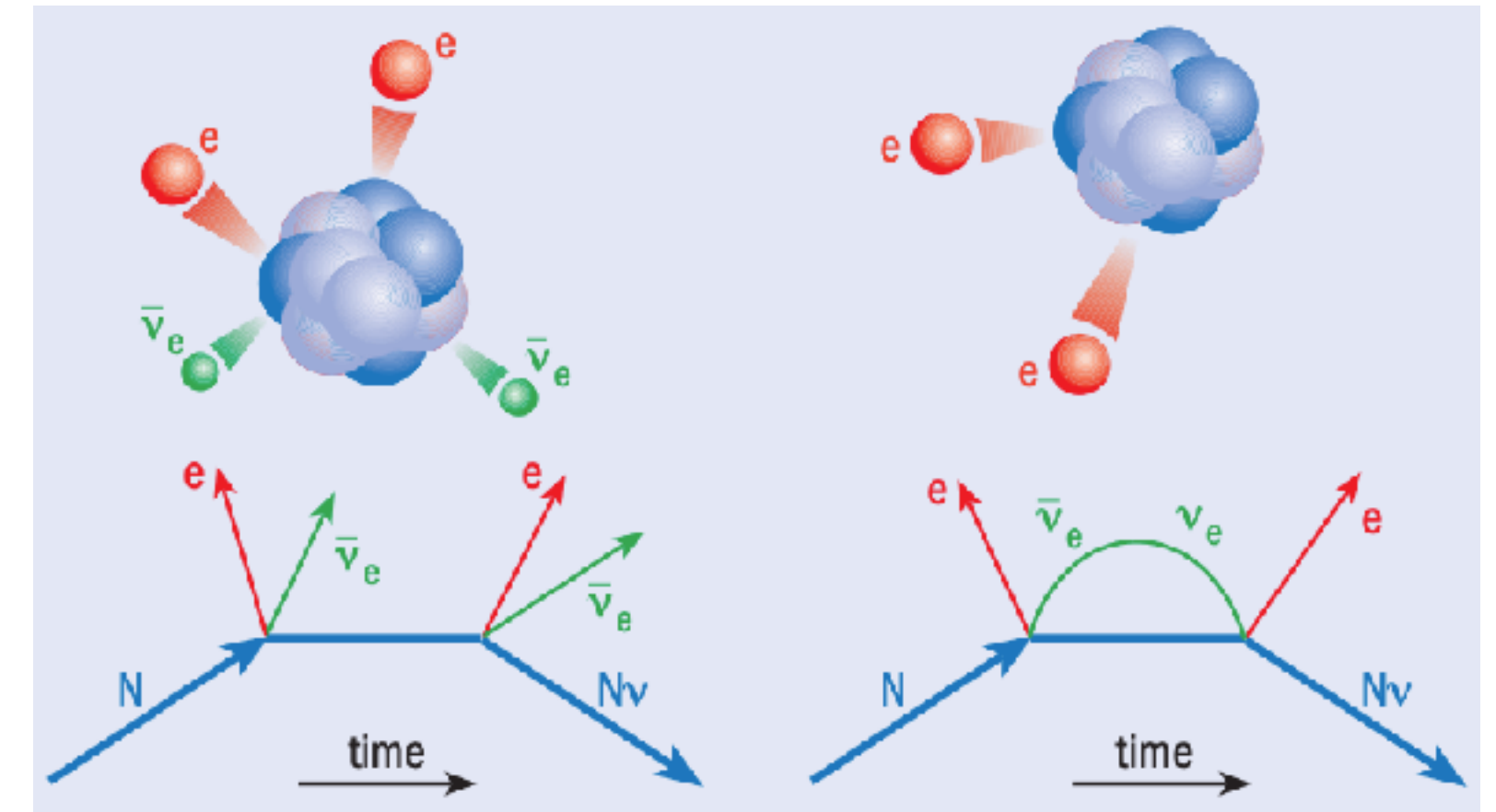
G. Gallina

for the nEXO collaboration

Overview

Motivation for ^{136}Xe Neutrinoless Double Beta Decay

- Finding $0\nu\beta\beta$ always implies new physics
- Lepton number violation
- Neutrinos are Majorana fermions ($\nu \equiv \bar{\nu}$)
- Origin of neutrino masses
- Insight into absolute neutrino mass scale
- Possibly linked to matter and anti-matter asymmetry
- Experimental signature is a peak at the Q-value (2458 keV for ^{136}Xe)



SiPM technology in nEXO

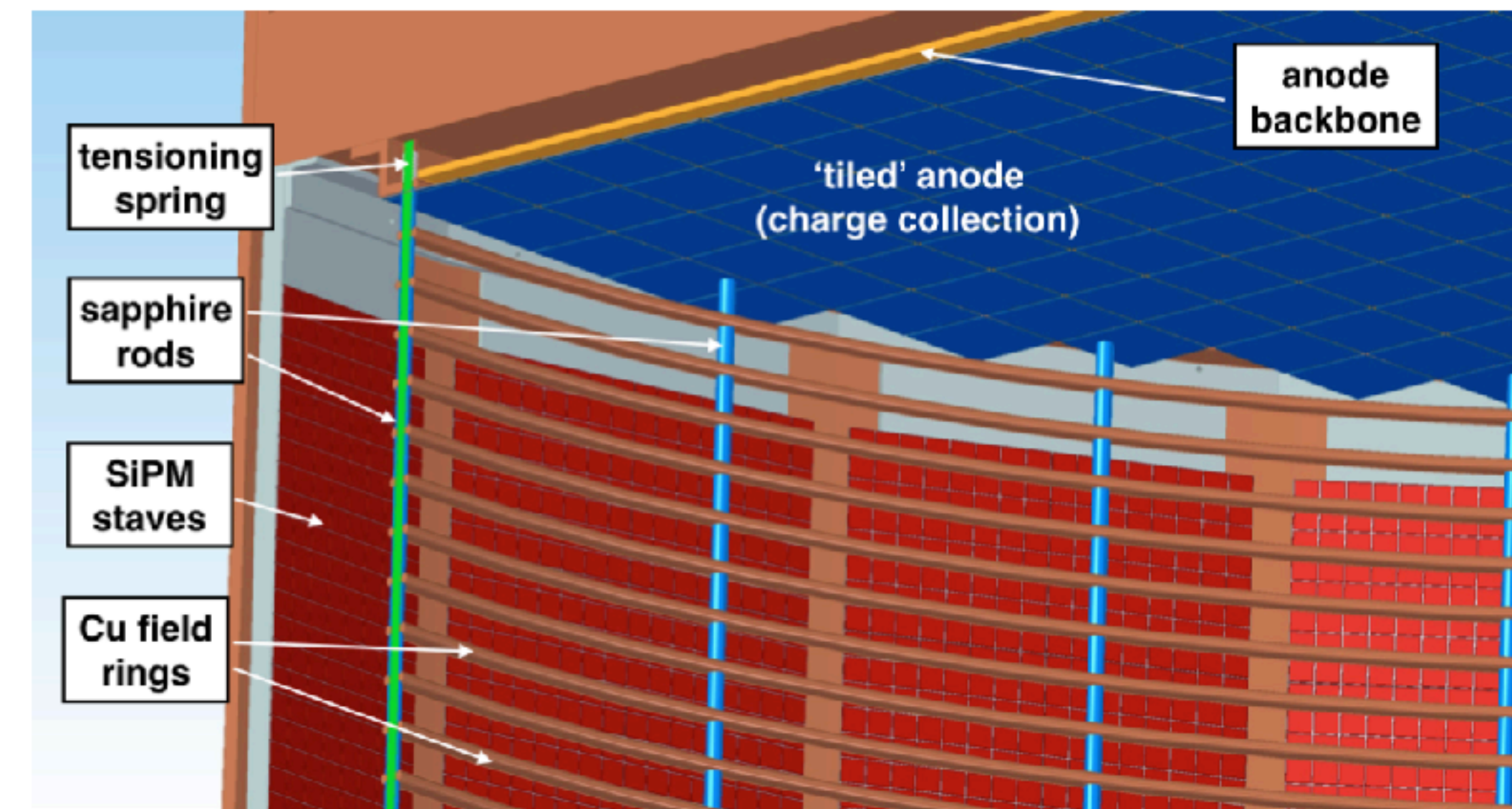
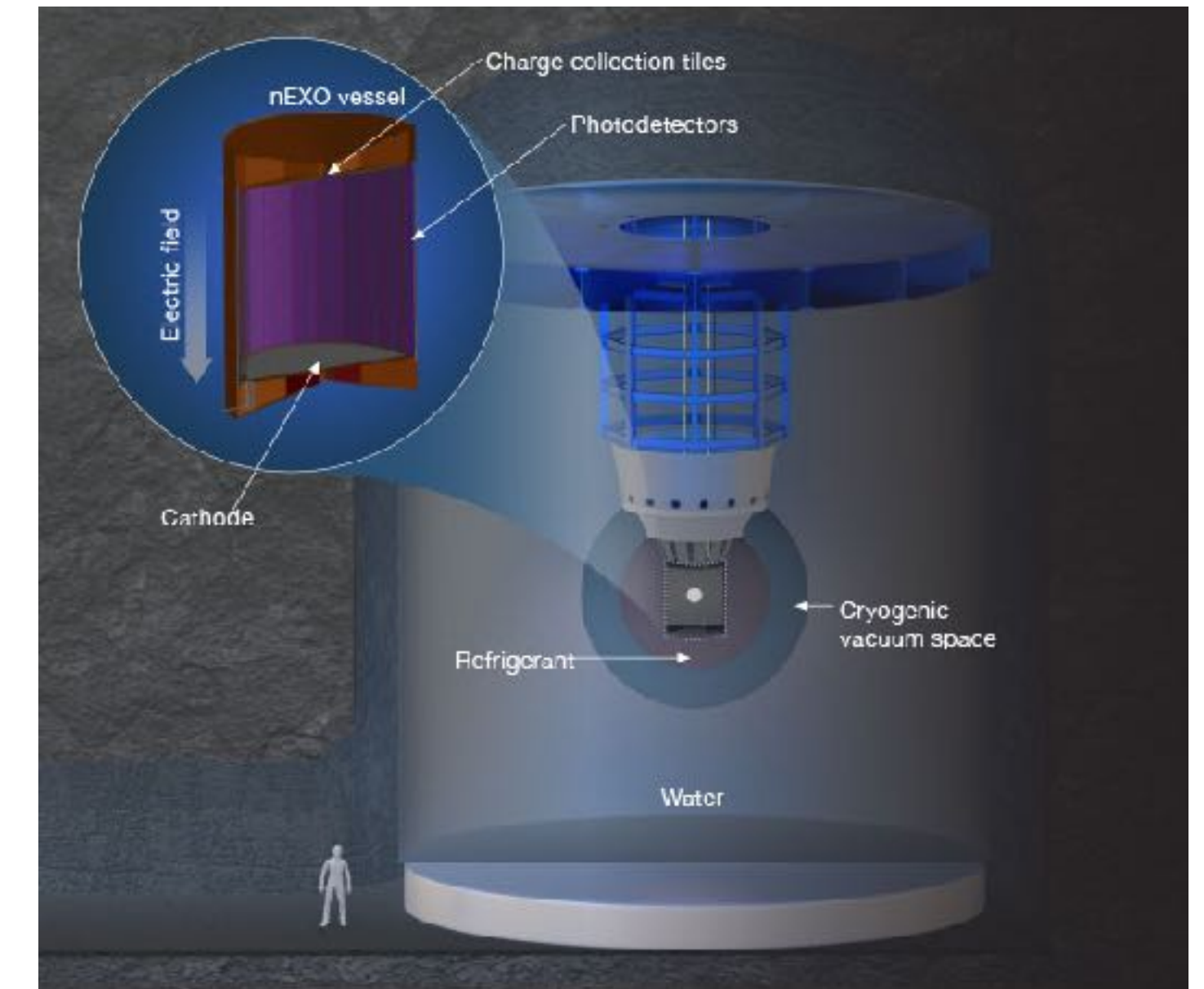
In nEXO we plan to use $\sim 4.5 \text{ m}^2$ covered with VUV-sensitive SiPMs

Main Characteristics :

- SPADs connected in parallel operated in reverse bias mode
- Incoming photon triggers charge avalanche
- Single pixel is discharged

Advantages:

- High gain at low bias voltage
- Single photon detection resolution
- High radio purity than PMTs possible
- Suitable at cryogenic temperature



SiPM technology in nEXO

NIM A 940 (2019)

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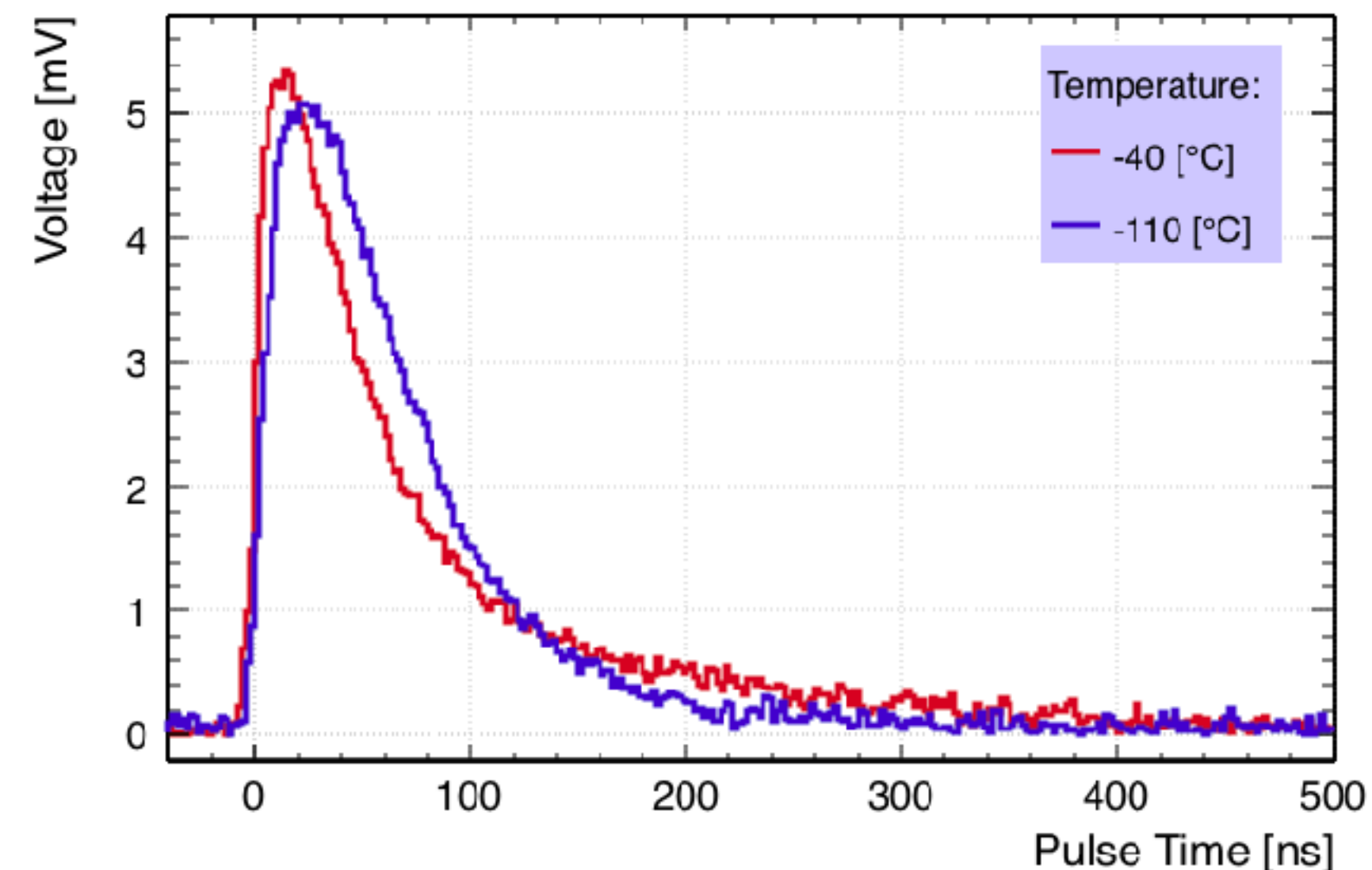
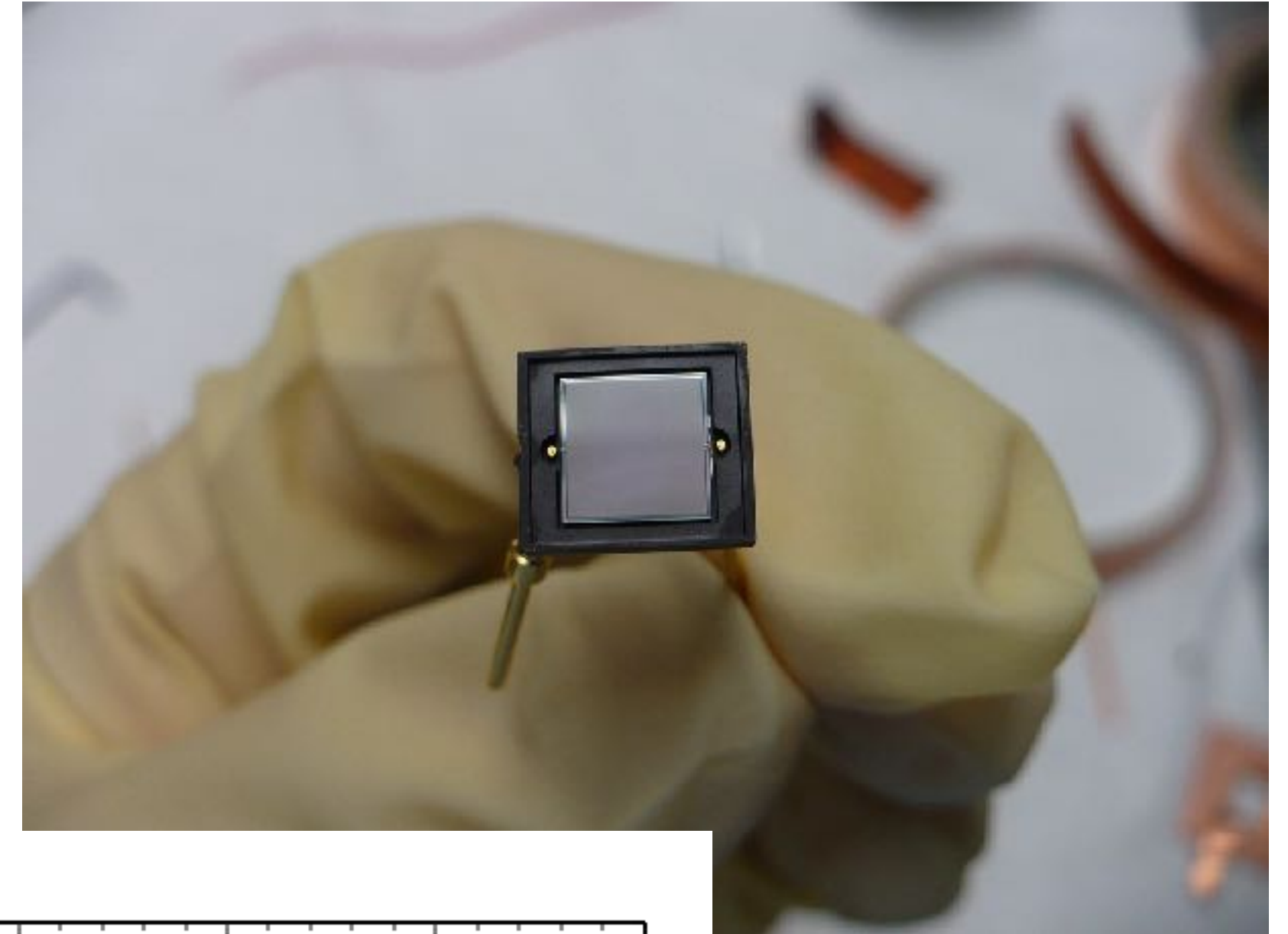
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Noise Sources in SiPMs

Uncorrelated Avalanche Noise

- Dark Count Rate (DCR)

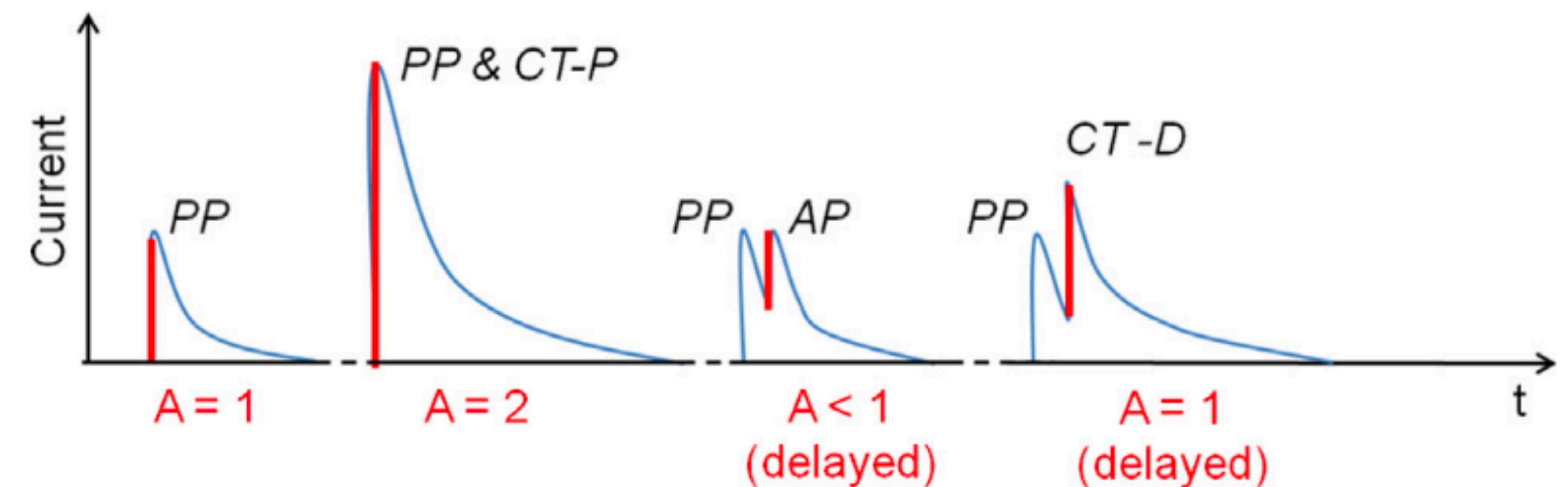
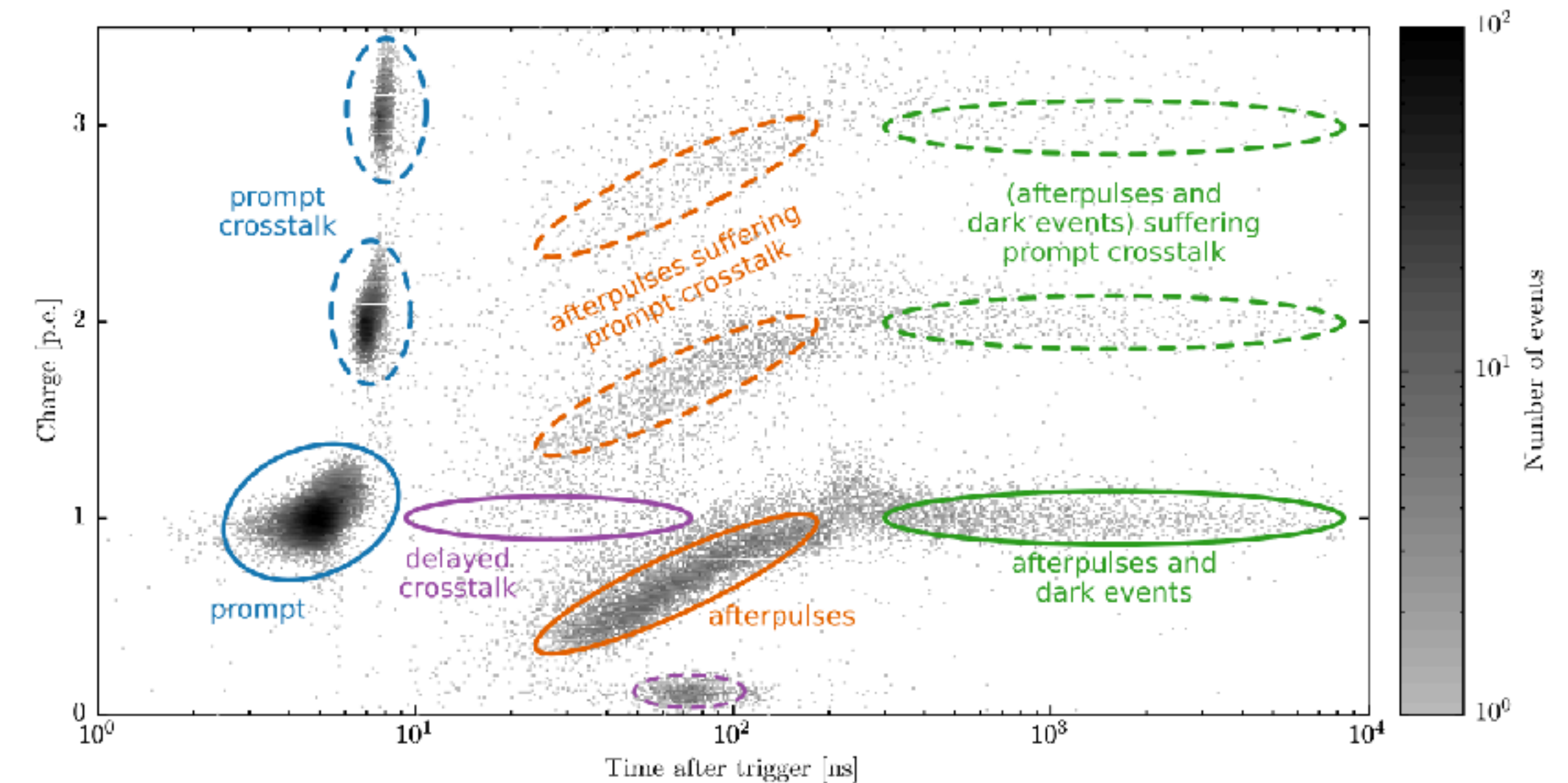
Correlated Avalanche Noise

- Afterpulse (AP)
- Internal Cross talk (CT)
- External CT

For Internal Cross Talk an additional discrimination is based on timing :

CT-P : Cross-Talk Prompt ($\ll 1$ ns)

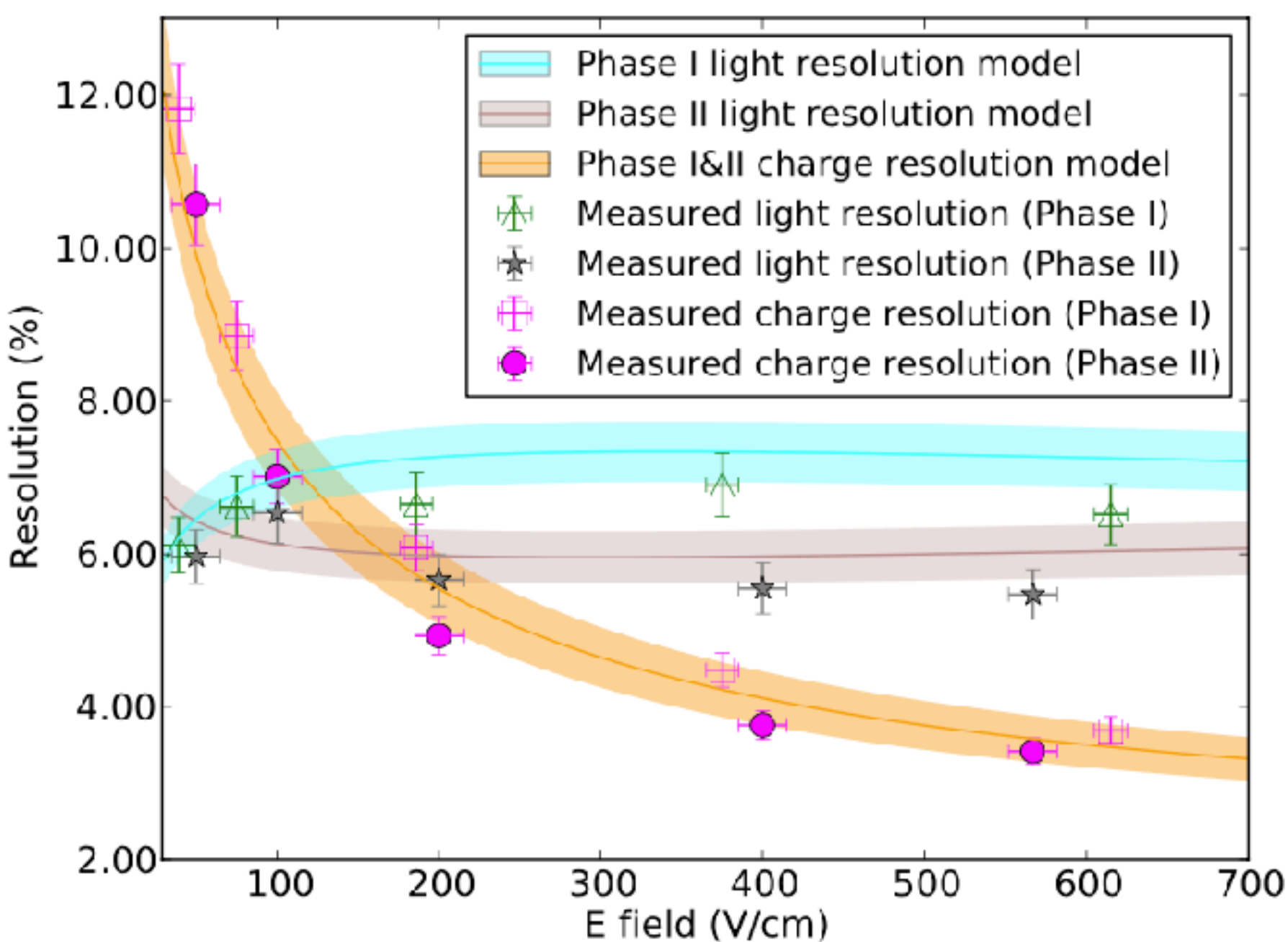
CT-D : Cross-Talk Delayed (> 1 ns)



Primary pulses (PP) with different types of correlated pulses such as prompt CT (CT-P), afterpulse (AP) and delayed CT (CT-D).

Rotated energy resolution is dominated by light collection efficiency

- Unlike charge, only <10 % of photons are collected
- Statistical fluctuation in collection drives overall nEXO resolution
- Understanding system level collection efficiency is key to accurately projection nEXO resolution
- Sub-dominat (but not negligible) contribution from fluctuation in correlated avalanches (CA)



Energy resolution measured with EXO-200

APDs at 2615 keV

Collection efficiency

$$\epsilon_P = \text{PTE} \times \text{CE} = \text{PTE} \times \frac{\text{PDE}}{1-R}$$

Photon transport efficiency (points to PTE)

Photon collection efficiency (points to CE)

Photon Detection efficiency (PDE) (points to PDE)

Reflectivity (R) (points to R)

Correlated avalanches

$$\frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

RMS of CA charge per PE (points to σ_{Λ})

Mean Charge in CA per primary PE (points to $\langle \Lambda \rangle$)

Uncorrelated avalanches

DCR

nEXO SiPM Requirements at 163 K

$$\text{CAF} \equiv \frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

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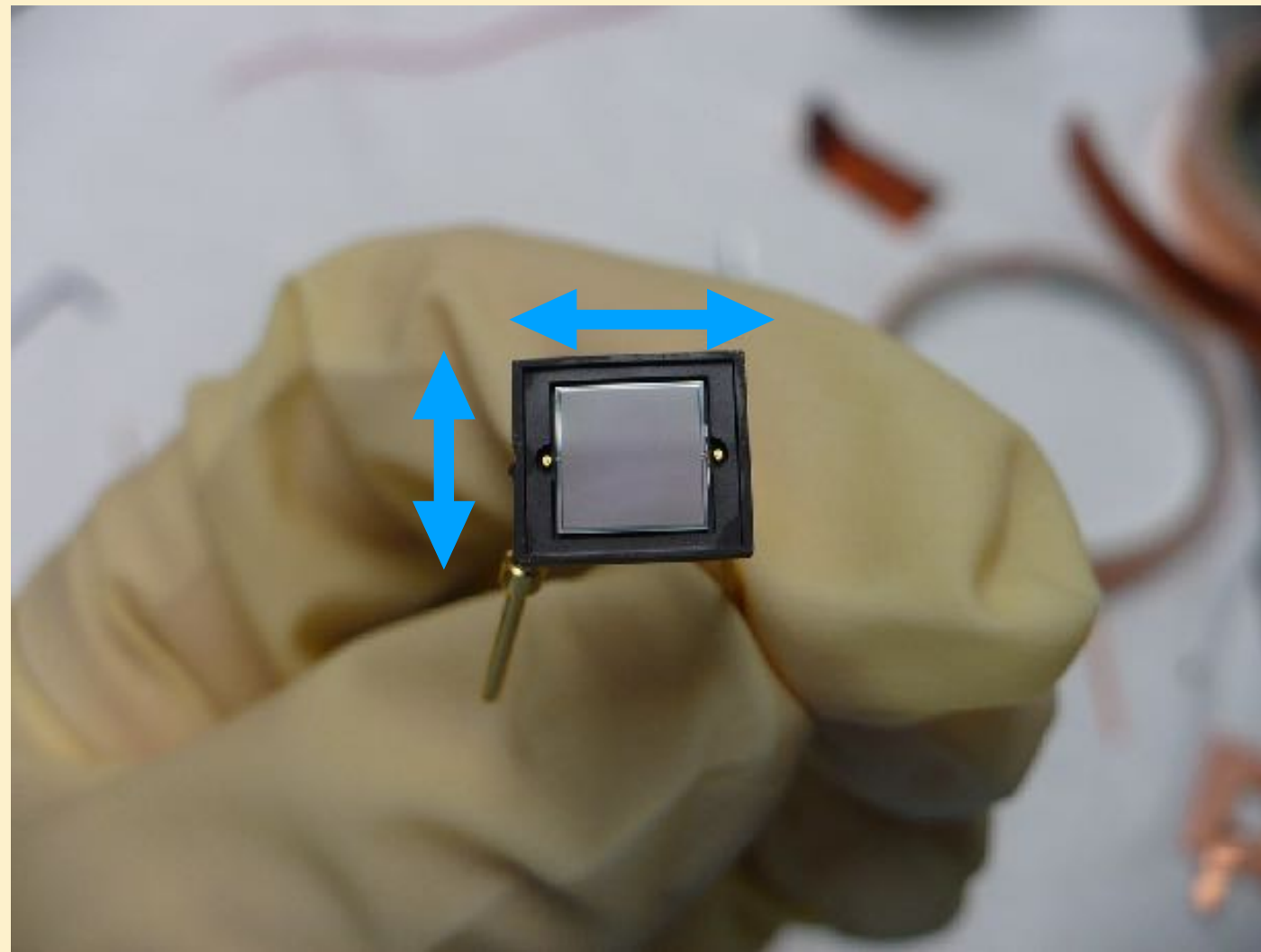
Parameters	Value
Photo-detection efficiency (PDE) at 175-178 nm in liquid Xenon	$\geq 15\%$
Radio purity: contribution of photo-detectors on the overall background	$< 1\%$
Dark noise rate at -110 °C	$\leq 10 \text{ Hz/mm}^2$
Correlated Avalanches fluctuation (CAF) per pulse in 1μs at -110 C	≤ 0.4
Single photo-detector active area	$\geq 1\text{cm}^2$
Operational gain	$\geq 1.5 \times 10^6 \text{ e}^-$
Capacitance per area	$< 50 \text{ pF/mm}^2$
Equivalent noise charge	$< 0.1 \text{ PE r.m.s}$

Three SiPMs analysed in this work: 2 Hamamatsu VUV4 MPPCs and FBK VUVHD3 SiPM

nEXO 6x6 mm² SiPMs candidates

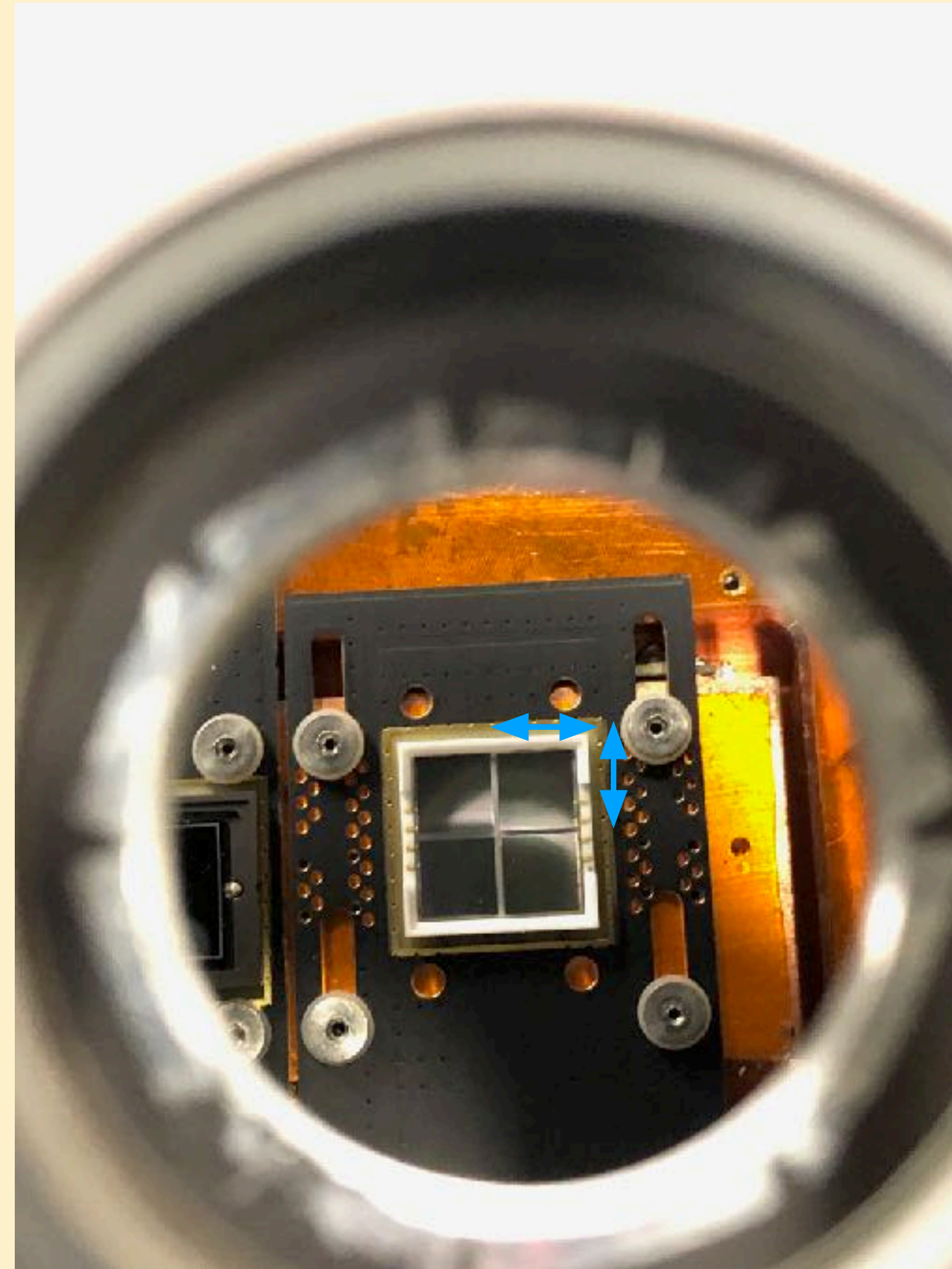
Hamamatsu MPPCs

NIM A 940 (2019)



HPK VUV4-50

Single devices
50 um pitch

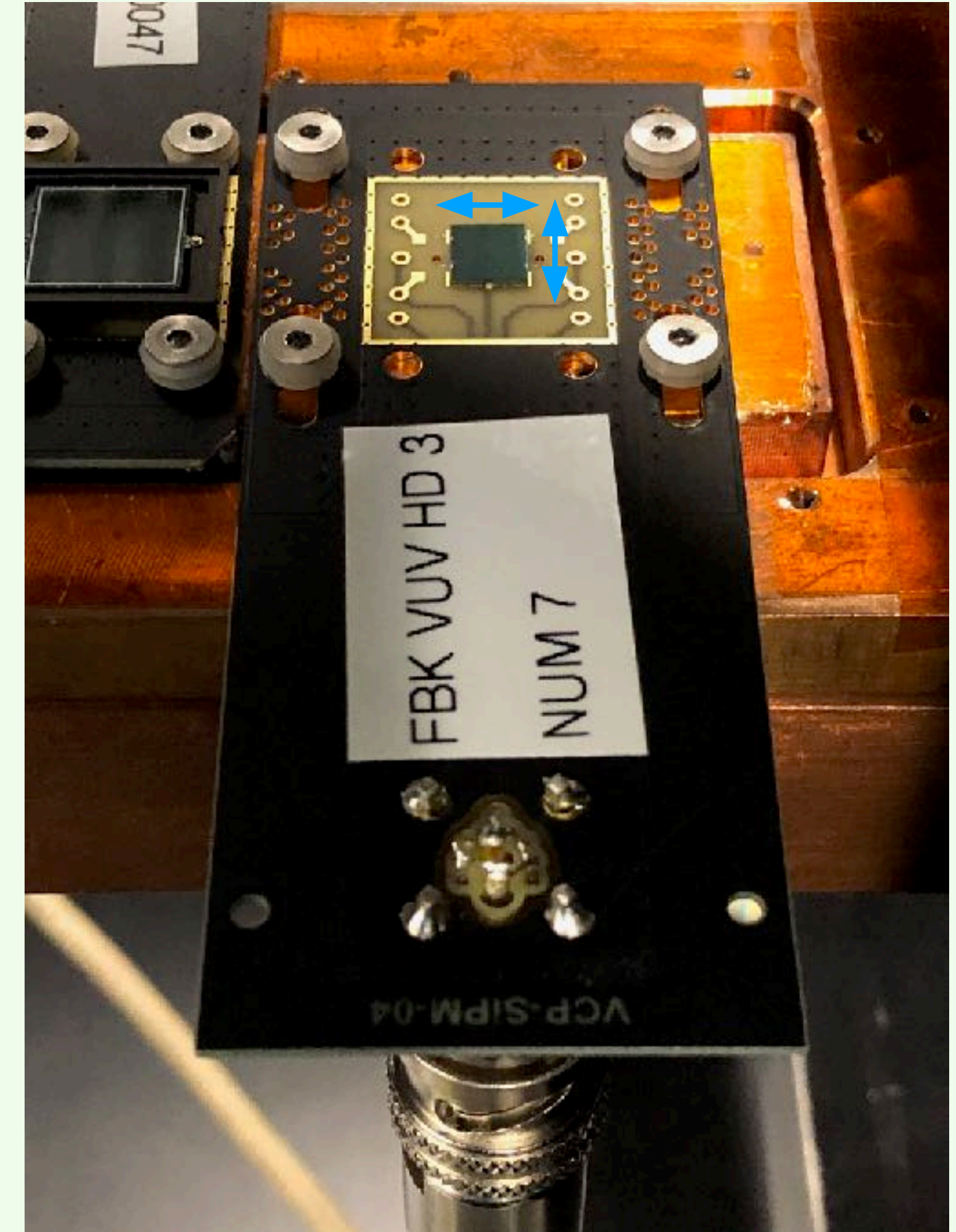


HPK VUV4-Q-50

Quad devices.
50 um pitch

IEEE Trans.Nucl.Sci. 65 (2018)

FBK SiPM



FBK VUVHD3

substitutes
its previous generation
FBK VUVHD1

An international joint effort

The nEXO photodetector team

- **This work** is part of a joint effort of the photodetector group where several institutions contributed to data taking and analysis
- It is the end of more than 2 years of data taking/analysis and comparison !

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TRIUMF

G. Gallina, F. Retiere, P. Margetak,
N. Massacret, M. Mahtab et al.

IHEP

G. Cao, Y. Guan et al.

YALE

A. Jamil, A. Bhat,
D. Moore

BNL/Drexel

A. Bolotnikov,
I. Kotov, A. Kumar et al.

UMass

A. Pocar, W. Gillis,
Reed C. et al.

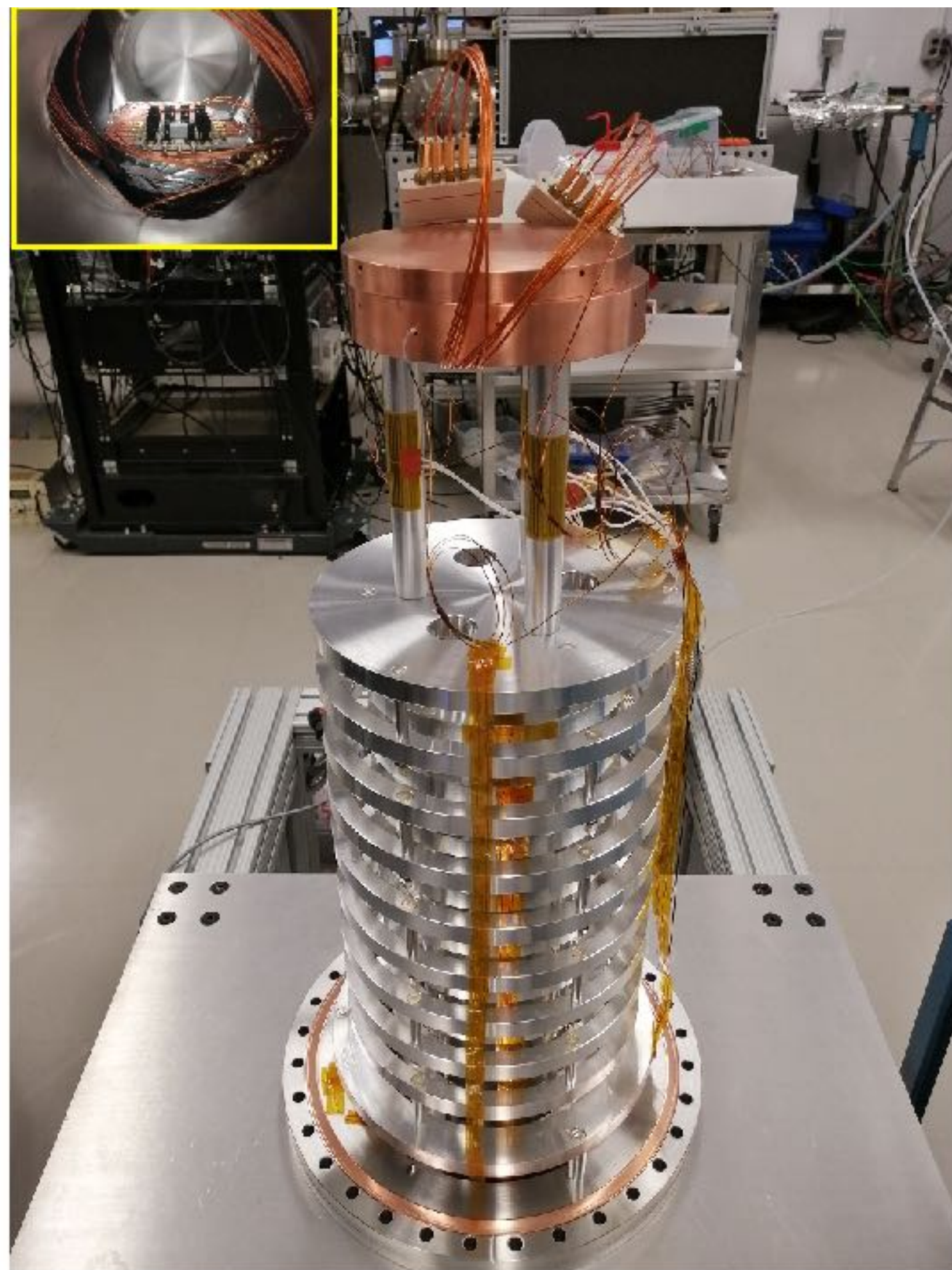
McGill

L. Darroch, T. Brunner et al.

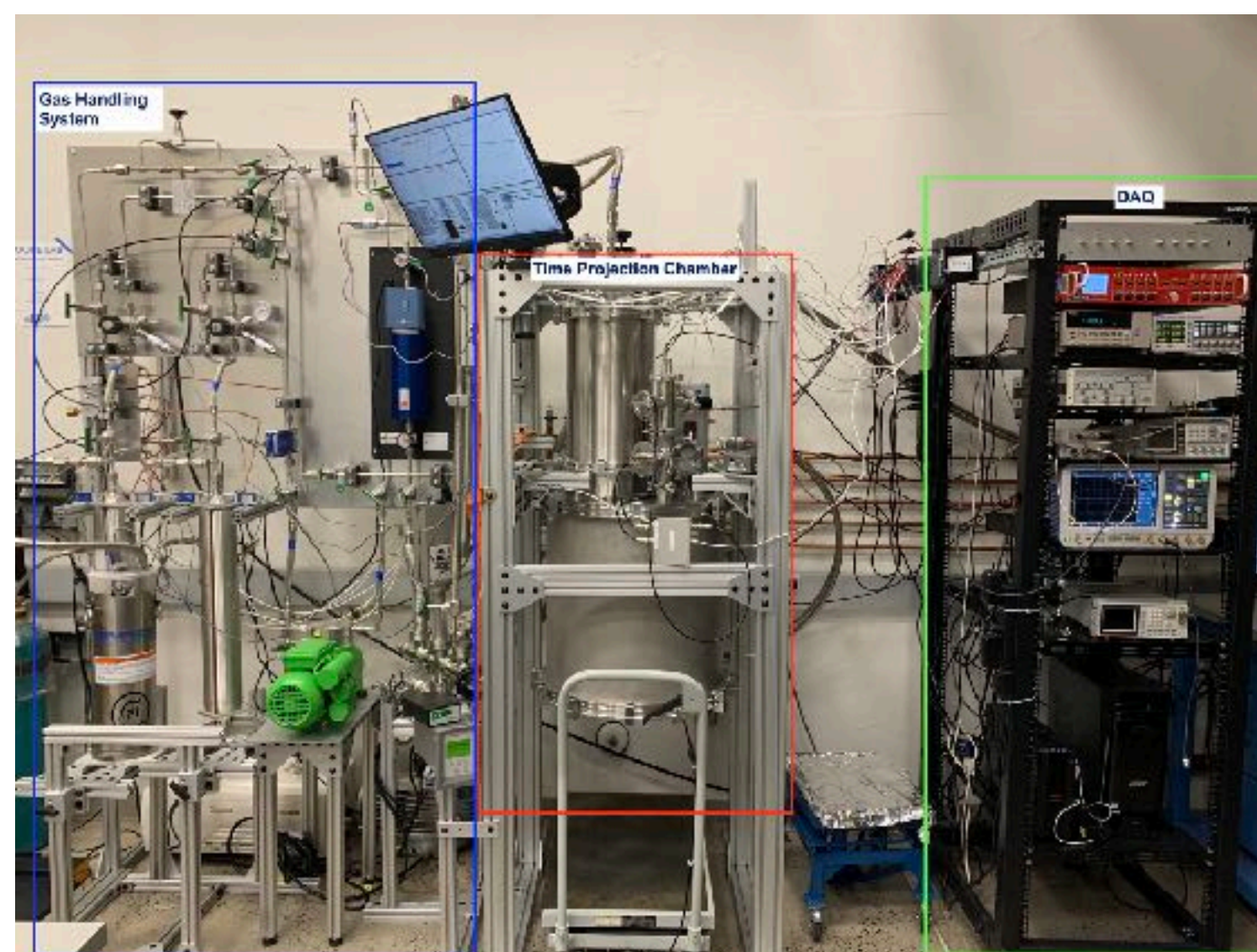
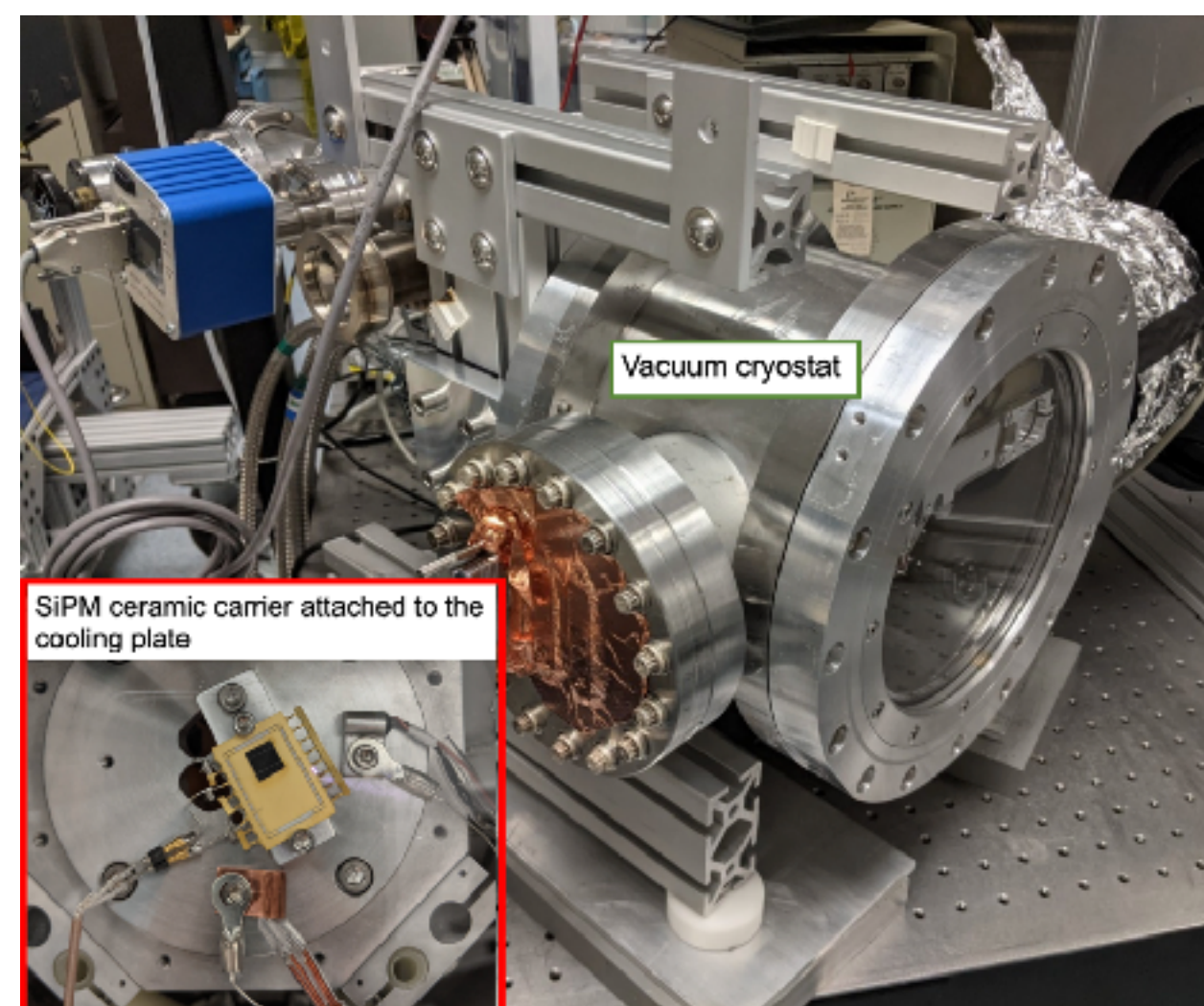
New measurements in EPJC ! [arXiv:2209.07765](https://arxiv.org/abs/2209.07765)

nEXO Testing setups: Dark measurements

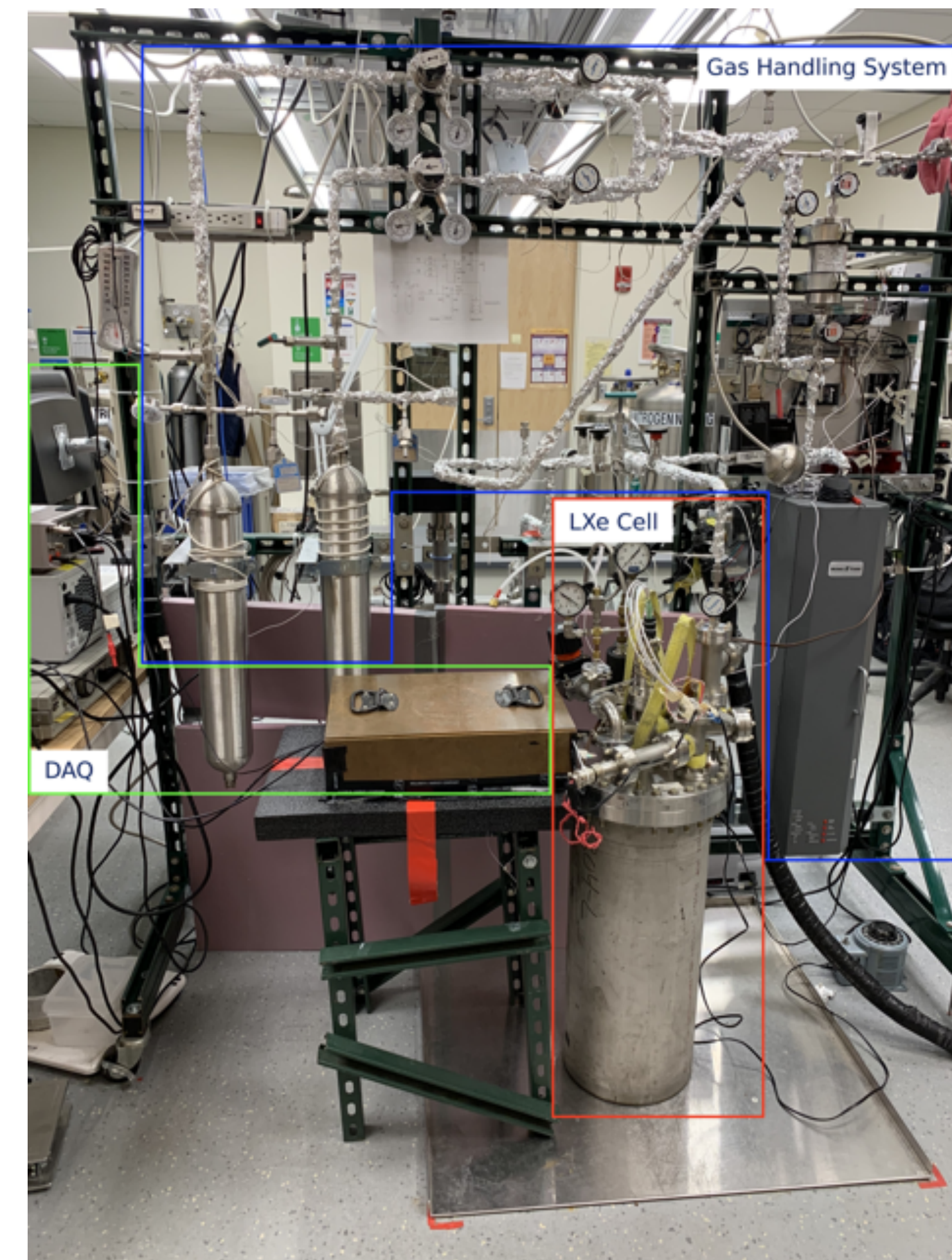
BNL Setup



McGill Setup



Yale LXe Setup

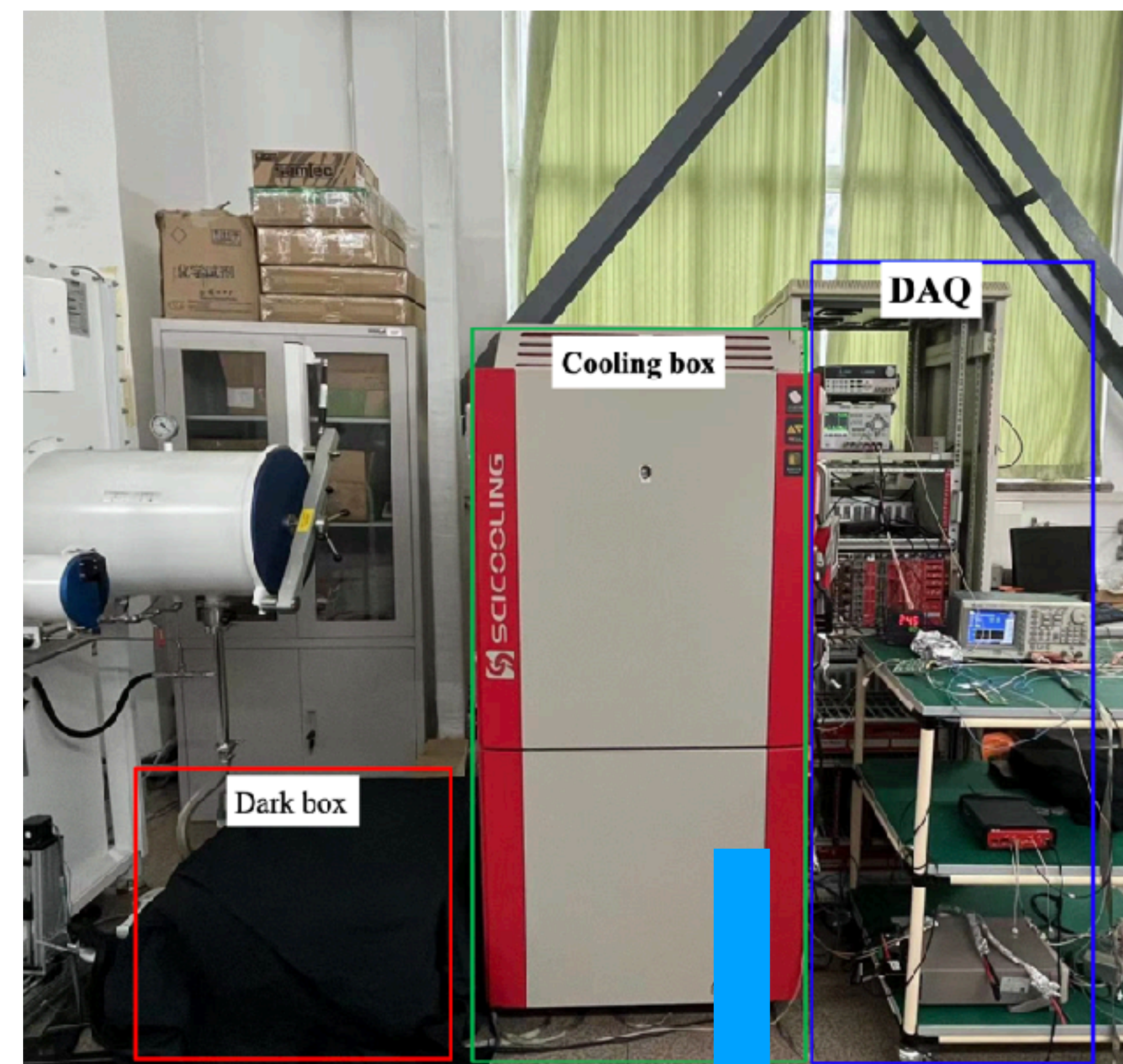


UMass LXe Setup

nEXO Testing setups: Dark and PDE measurements



TRIUMF Setup



IHEP Setup

- Both setups are equipped with vacuum monochromators.
- IHEP PDE measurements are done at 233 K, TRIUMF ones at 163 K



Dark Count Rate (DCR)

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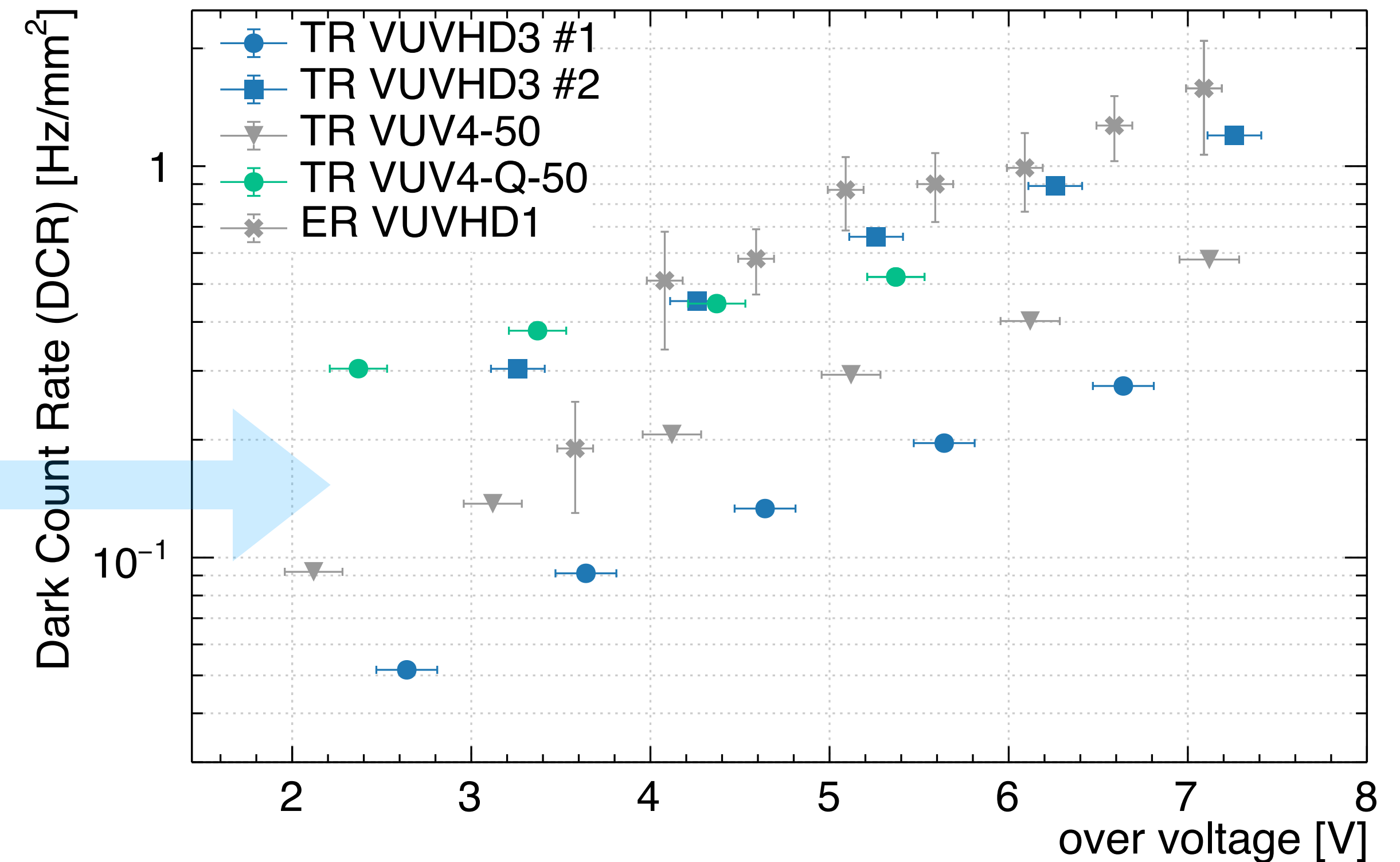
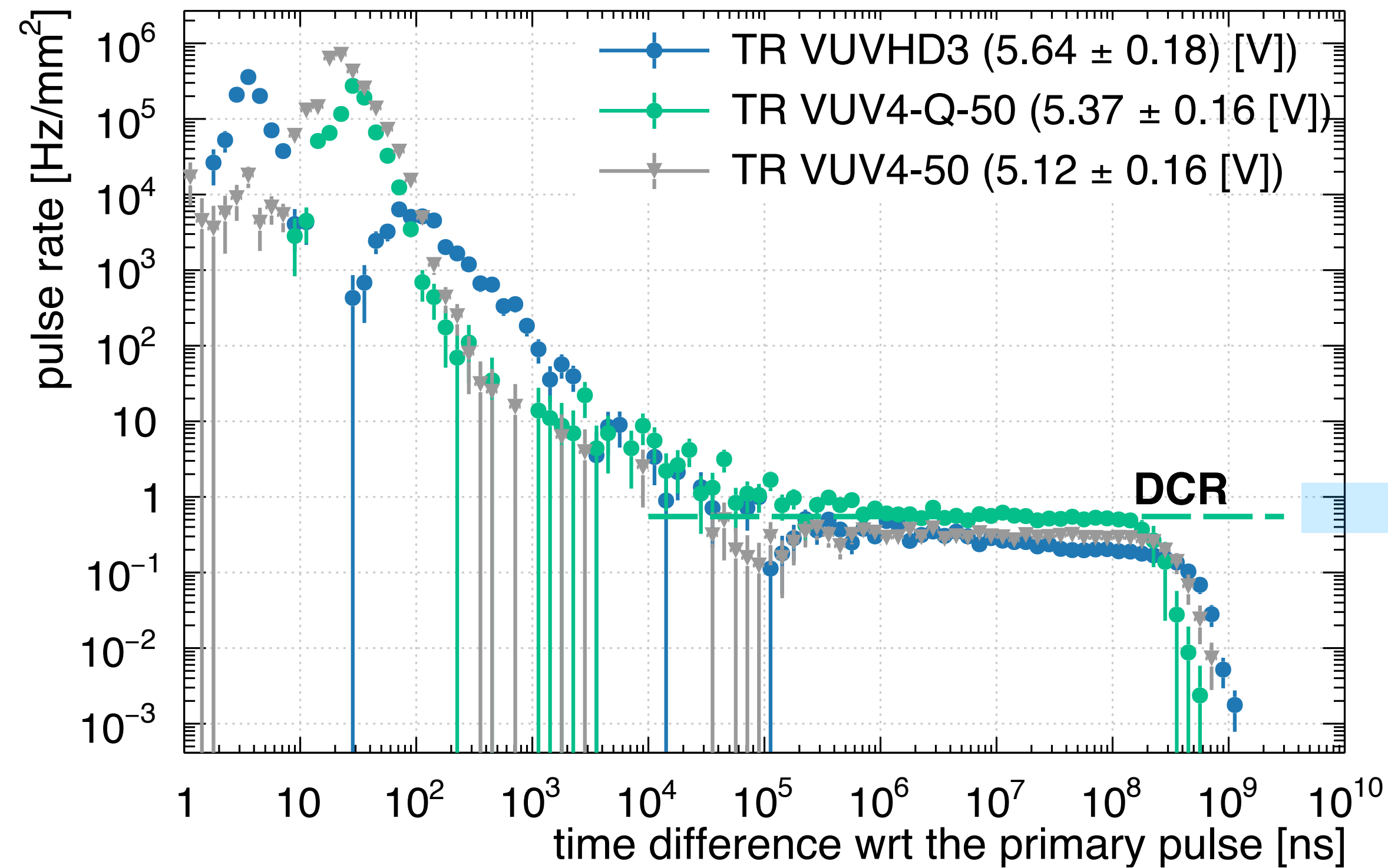
Grey points !

NIM A 940 (2019)

IEEE Trans.Nucl.Sci. 65 (2018)

Computed using time differences between pulses as shown in 10.1016/j.nima.2017.08.035

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Requirement at 163 [K]: DCR < 10 Hz/mm²

- Requirement met in the entire range of OV studied!

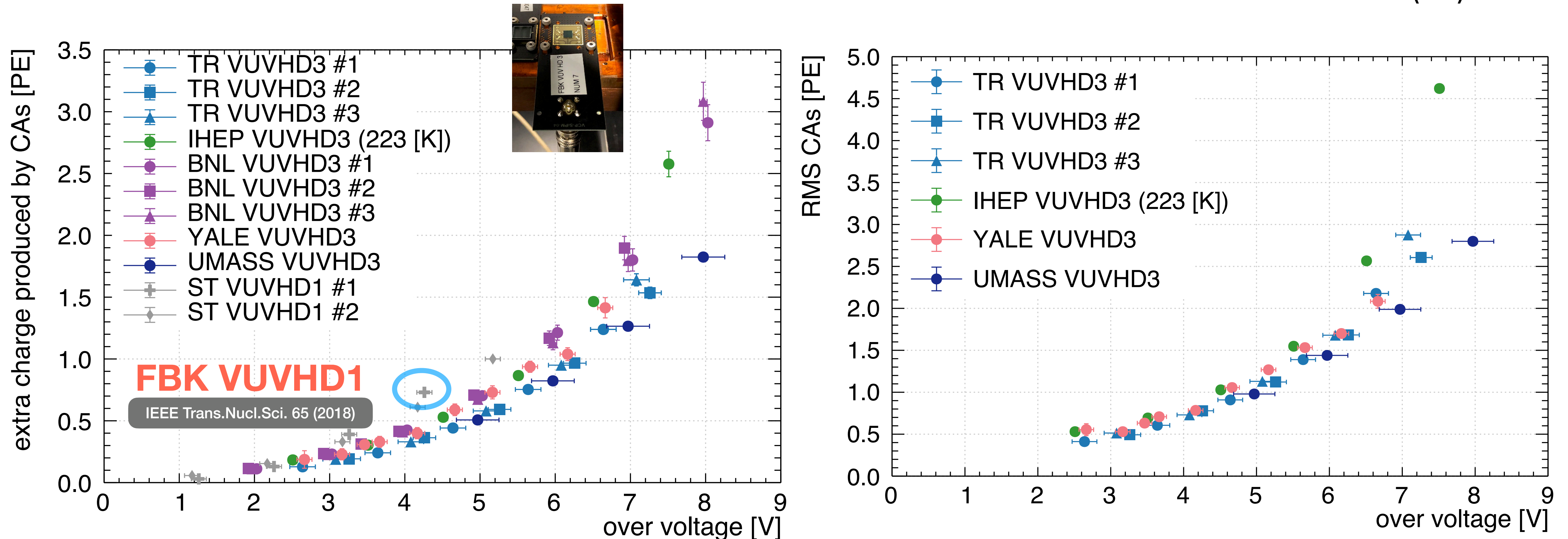
Correlated Avalanches

Correlated Avalanches FBK VUVHD3

- Defined as the ratio between the RMS (σ_{Λ}) and the mean $\langle \Lambda \rangle$ extra charge procured by correlated avalanches (CA) per pulse

$$\mathbf{CAF} \equiv \frac{\sigma_{\Lambda}}{1 + \langle \Lambda \rangle}$$

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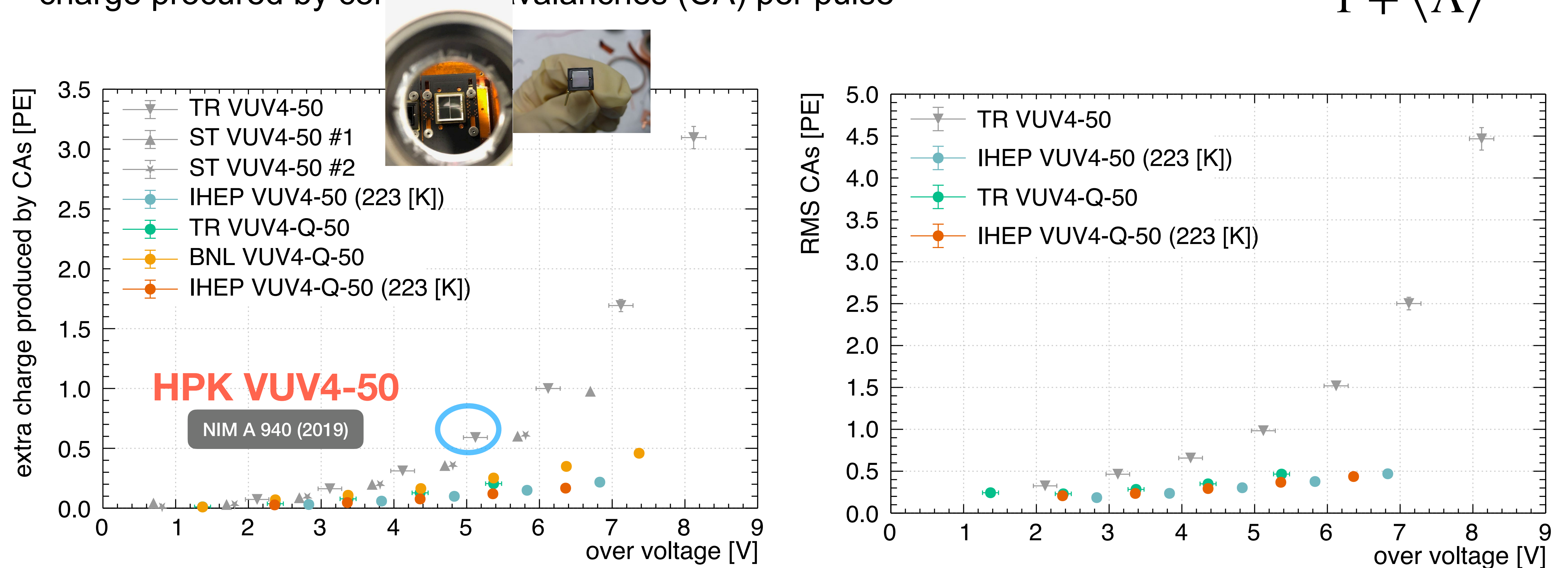
- FBK VUVHD3** is improved compare to **FBK VUVHD1**.

Correlated Avalanches HPK VUV4 MPPCs

- Defined as the ratio between the RMS (σ_Λ) and the mean $\langle \Lambda \rangle$ extra charge procured by correlated avalanches (CA) per pulse

$$\mathbf{CAF} \equiv \frac{\sigma_\Lambda}{1 + \langle \Lambda \rangle}$$

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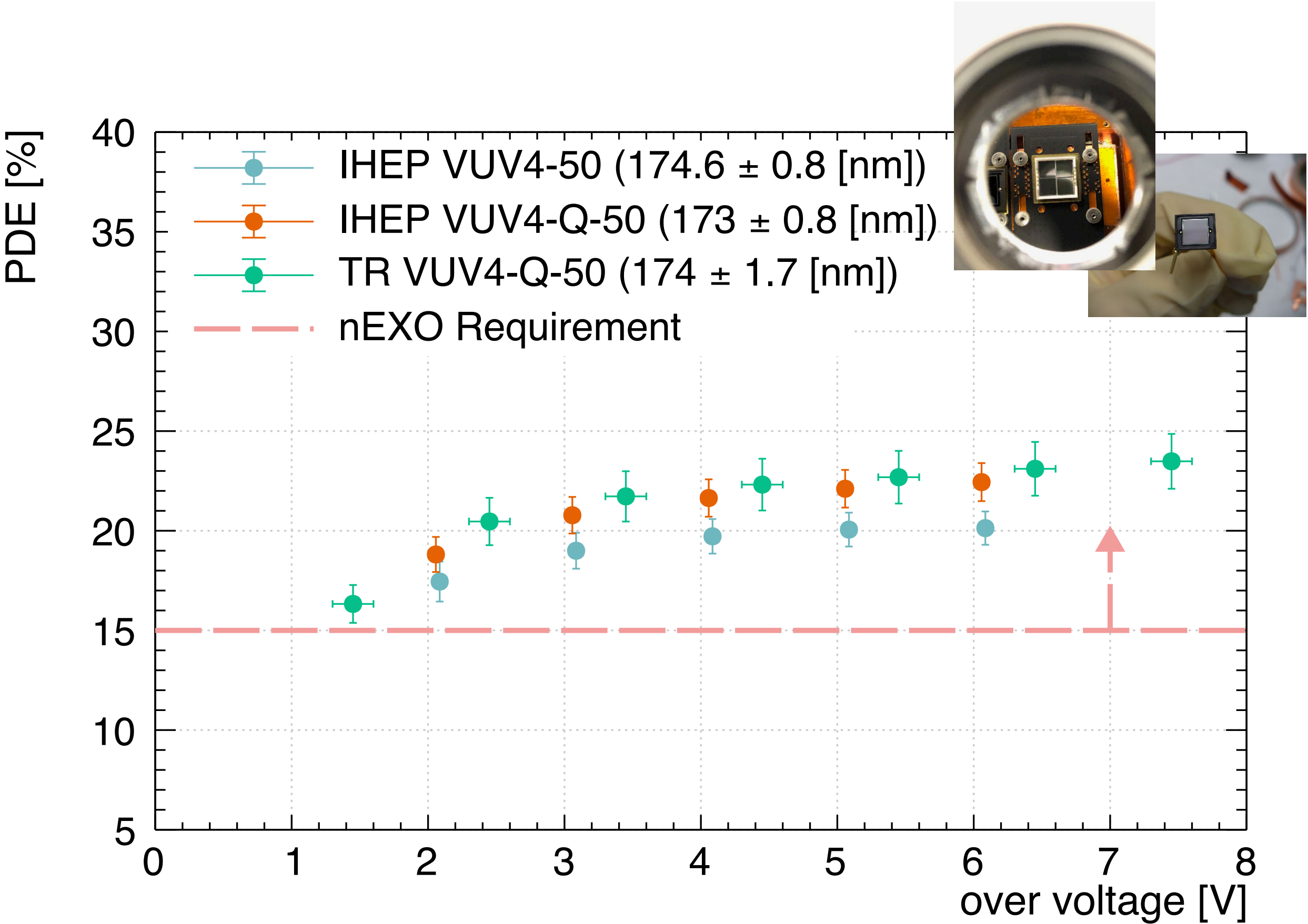
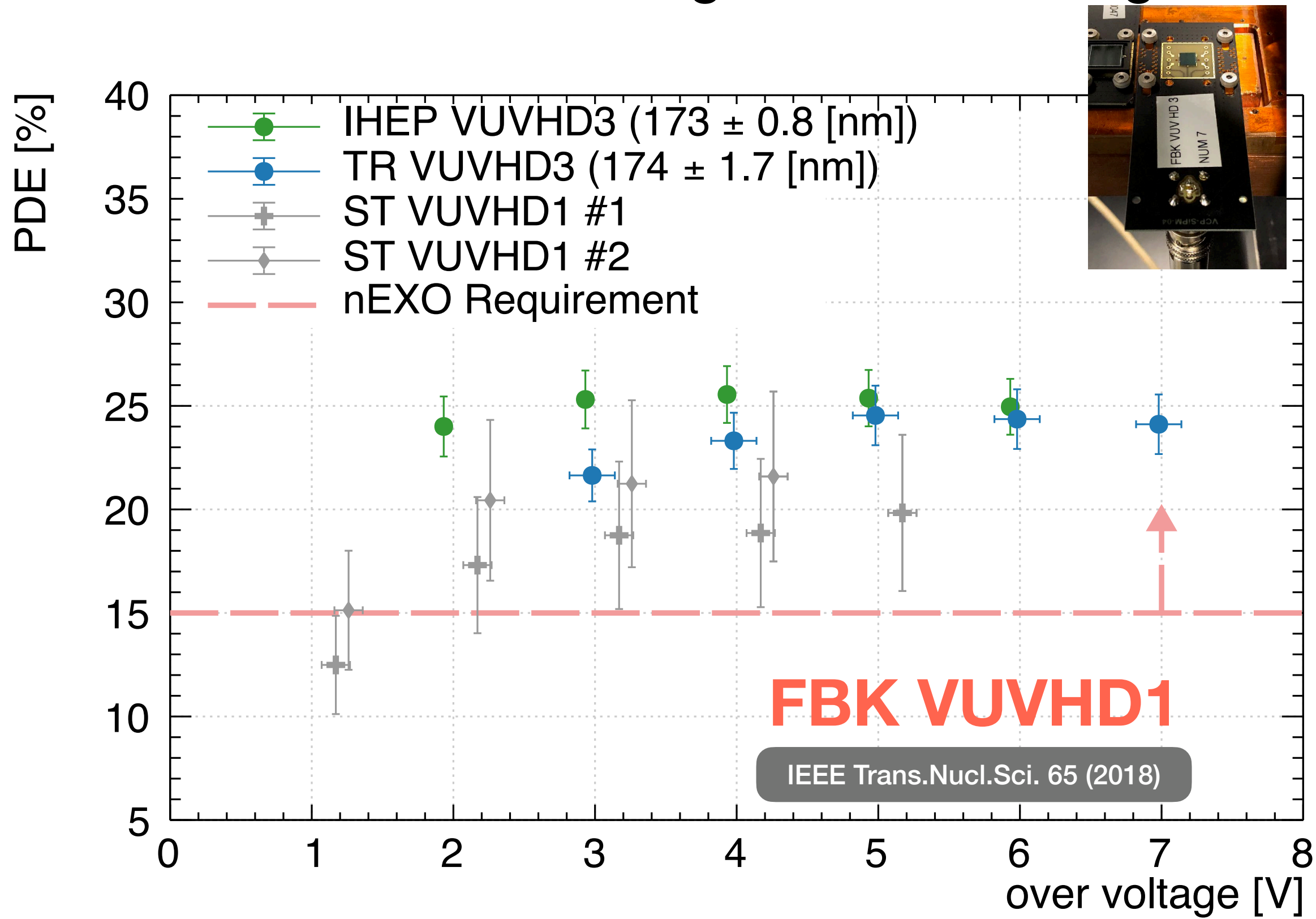


- HPK VUV4** has almost no correlated avalanches (CA) and it is significantly better than the **HPK VUV4-50** tested previously

Photon Detection Efficiency (PDE)

Photon Detection Efficiency (PDE) at 174 nm at 163 K

- PDE has been measured by TRIUMF and IHEP at 163 K and 233 K, respectively as a function of over voltage and wavelength



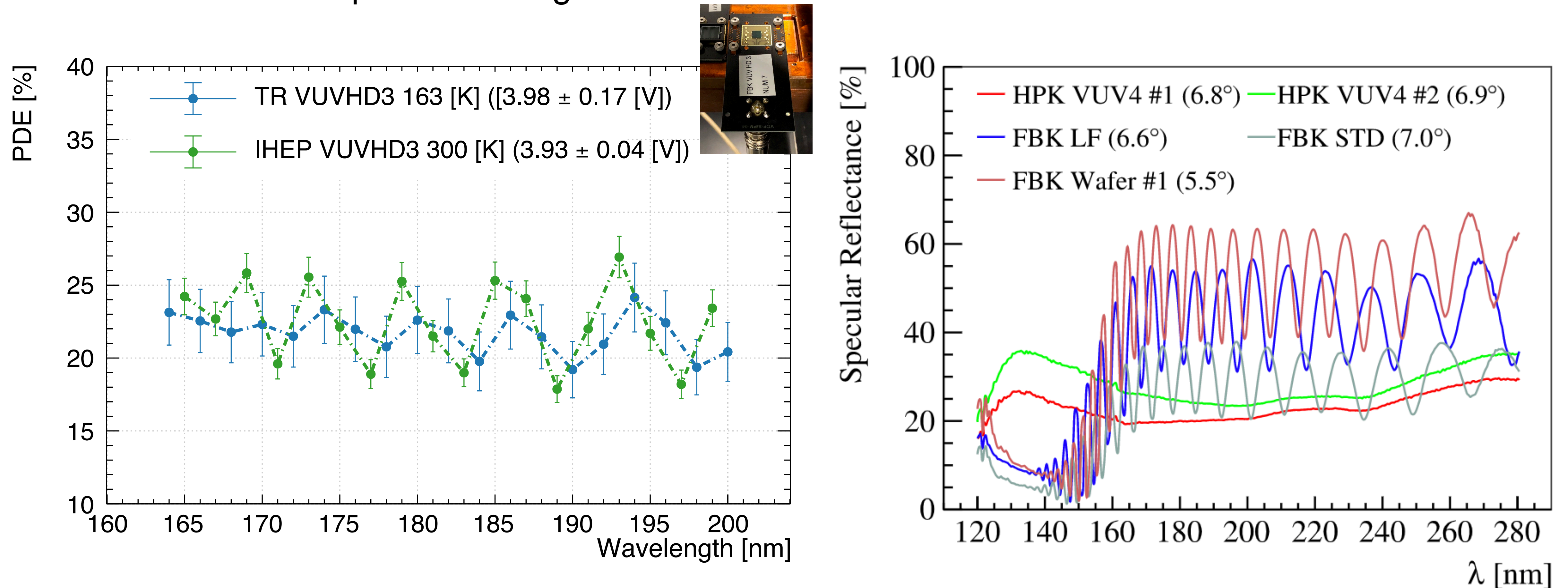
Requirement > 15% at ~ 175 nm

Requirement met from 1.5 V of OV !

Photon Detection Efficiency (PDE) Wavelength Dependence

21

- LXe scintillation spectrum is a gaussian with a mean of 174.8 nm and a STD of 4.33 nm

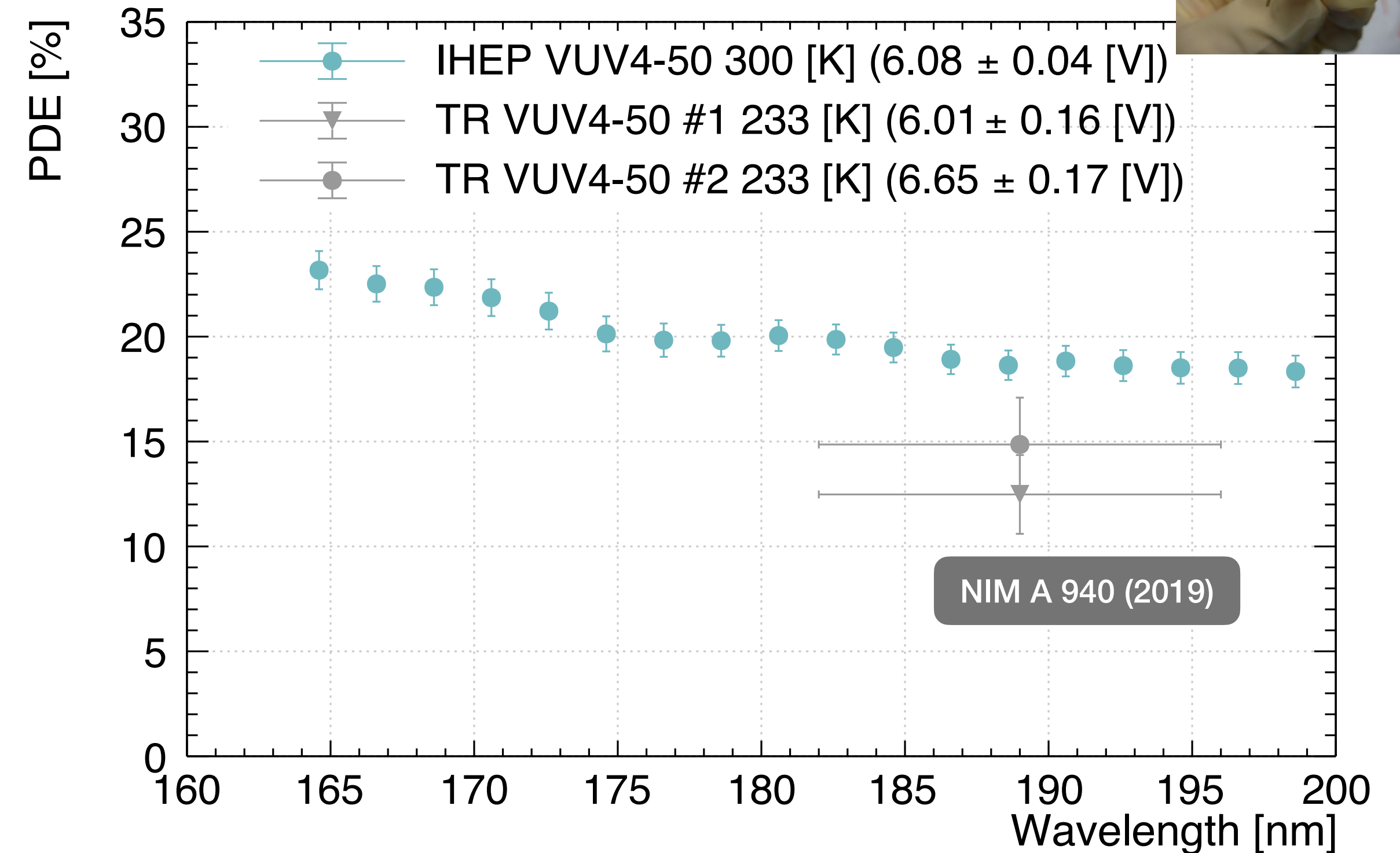
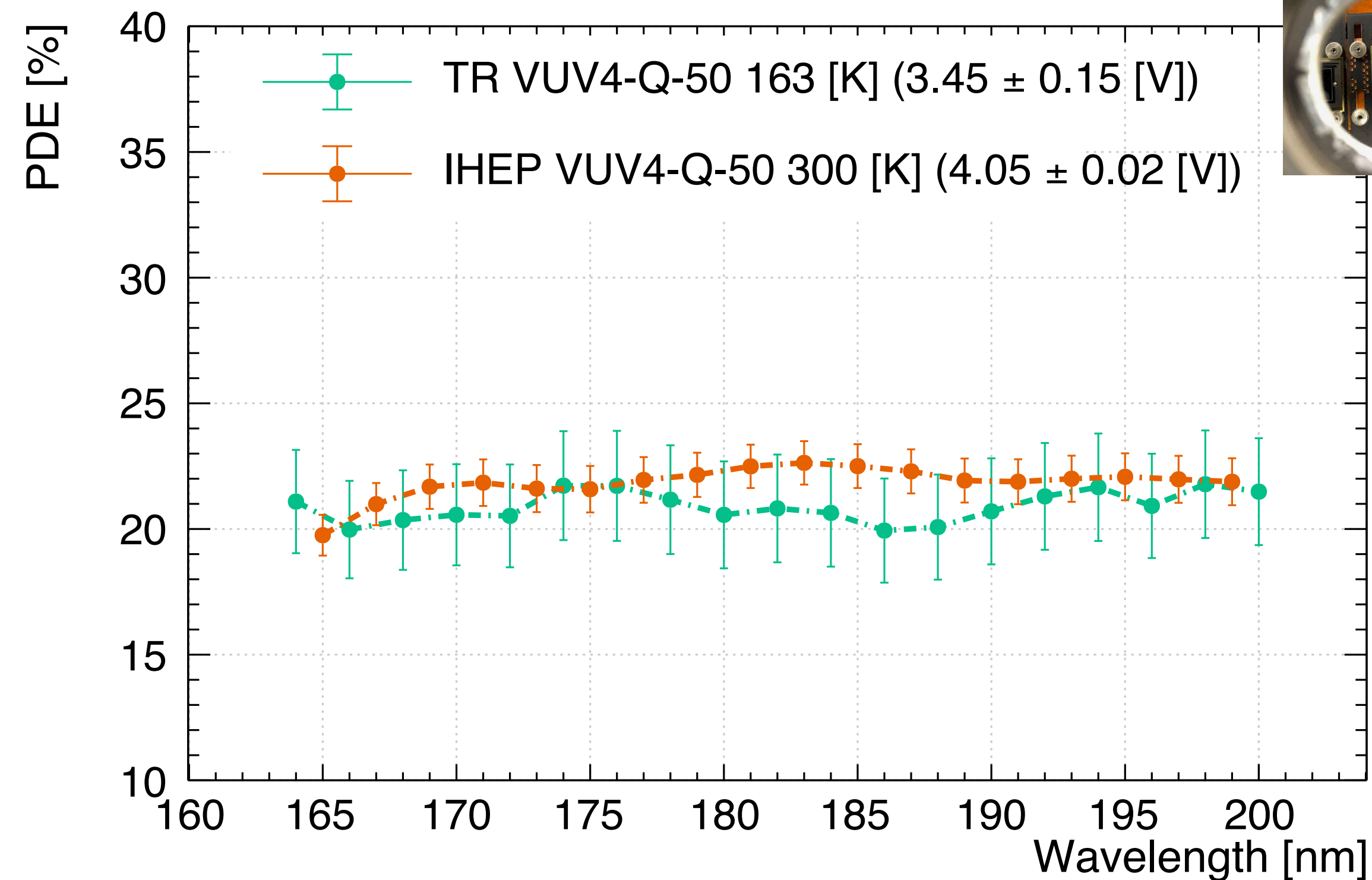


- FBK thin film interference in the SiO₂ top layer. Compatible with specular reflectivity measurements done at IHEP and published in 10.1109/TNS.2020.3035172

Photon Detection Efficiency (PDE) Wavelength Dependence

- LXe scintillation spectrum is a gaussian with a mean of 174.8 nm and a STD of 4.33 nm

22



- HPK MPPCs Quad devices have an efficiency higher of the corresponding single package 50um pitch device

Estimation of the nEXO Energy Resolution

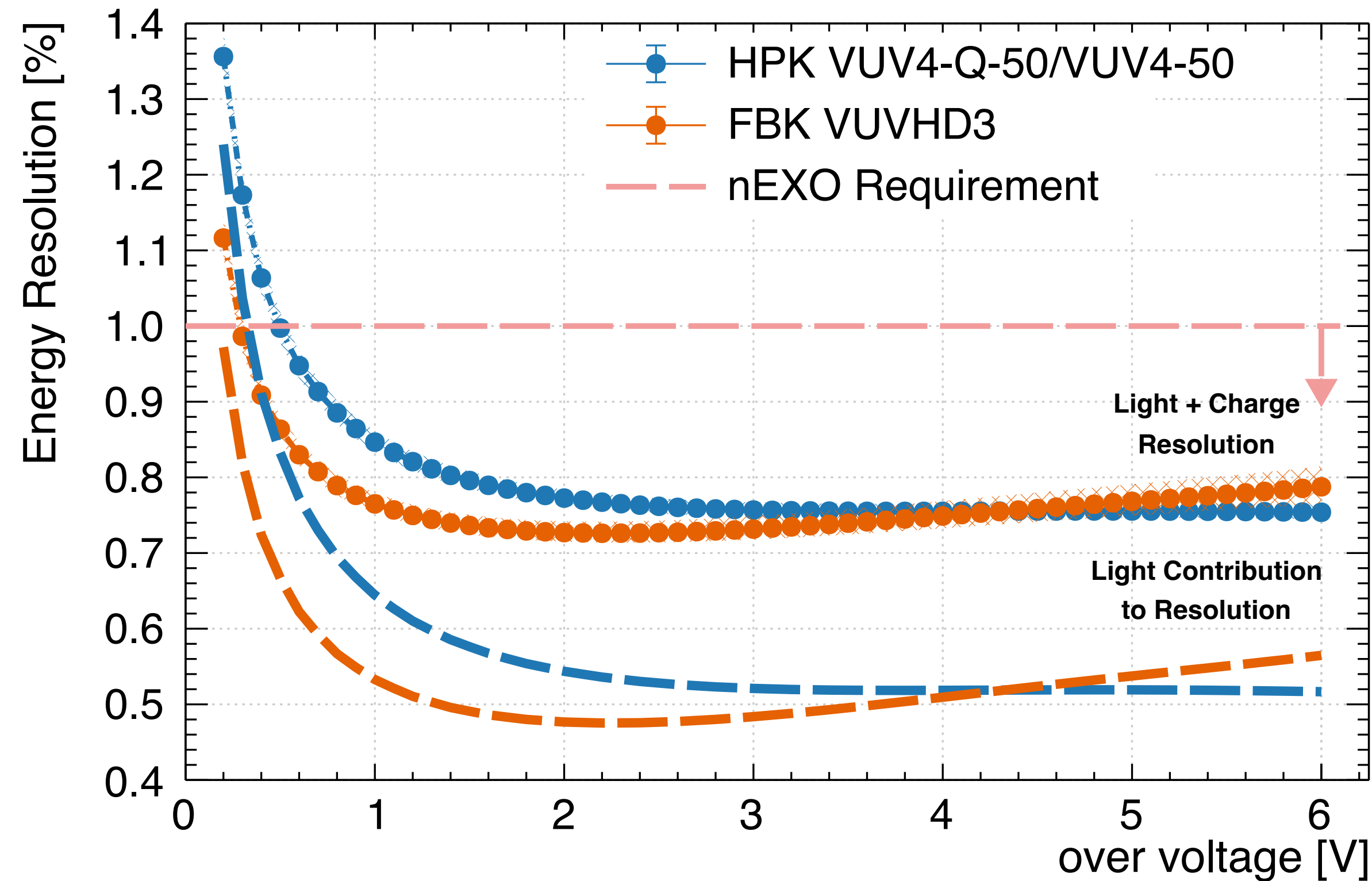
nEXO Energy Resolution at (2458 keV for ^{136}Xe)

arXiv:2209.07765

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$$\frac{\sigma_n}{\langle n \rangle} = \frac{\sqrt{\left(\frac{(1 - \epsilon_p)n_p}{\epsilon_p} + \frac{n_p}{\epsilon_p} \cdot \frac{\sigma_\Lambda^2}{(1 + \langle \Lambda \rangle)^2} + n_p^2 \sigma_{lm}^2 \right) + \left(\frac{n_q t}{\tau} + \frac{\sigma_{q,noise}^2}{\epsilon_q^2} \right)}}{\langle n \rangle}$$

$$\text{nEXO Requirement: } \frac{\sigma_n}{\langle n \rangle} \leq 1 \%$$



- eCT is not yet accounted. It may produce a slightly steeper rise.
- Not expected to impact the minimum

Fluctuation due to number of photons detected (PDE)

Fluctuation Due to Correlate Avalanche Noise (CA/RMS)

Residual Calibration Uncertainty

Fluctuation due to the number of charges detected

Fluctuation due to electronic noise in charge channel

Conclusions

Conclusions

- Presented a complete set of measurements with good agreement between several inst. !
- The three photosensors tested look to be excellent candidates for nEXO to reach sub-percent energy resolution
- Significantly more information is now available (PDE wavelength dependence etc ..) compared to what was previously known.
- More measurements are available than what was shown today (i.e. gain and Vbd as a function of bias voltage and temperature, respectively, CDA, APA etc ..)

Thanks !

G. Gallina^{1,2,3}, Y. Guan^{4,5}, F. Retiere⁶, G. Cao^{7,8,9}, A. Bolotin¹⁰, I. Kozlov¹¹, S. Rescia¹², A.K. Soma¹³, T. Tsang¹⁴, L. Darroch¹⁵, T. Branson¹⁶, J. Bolster¹⁷, J. R. Colson¹⁸, T. Piro Franco¹⁹, W. C. Gilje²⁰, H. Pella Smiley²¹, S. Thibault²², A. Poca²³, A. Bhat²⁴, A. Jami²⁵, D. C. Moore²⁶, G. Adhikari²⁷, S. Al Khawari²⁸, E. Angelico²⁹, L. J. Aronquist³⁰, P. Aronow³¹, I. Budnikov^{32,33}, J. Bane³⁴, V. Bobov³⁵, E. C. Bernard³⁶, T. Blatnik³⁷, E. A. Bryan³⁸, J. E. Brudsky³⁹, E. Brown⁴⁰, E. Caderni^{41,42}, L. Cao⁴³, C. Chaudhary⁴⁴, R. Chams⁴⁵, S. A. Charlebois⁴⁶, H. Chen⁴⁷, M. Chin⁴⁸, B. Cleveland^{49,50}, R. Collister⁵¹, M. Cvetani⁵², J. Dalmas⁵³, T. Daniels⁵⁴, K. Delamater⁵⁵, R. DeVoe⁵⁶, M. L. di Vacri⁵⁷, Y. Ding⁵⁸, M. J. Dolinski⁵⁹, A. Dragone⁶⁰, J. Echeverez⁶¹, B. Ecker⁶², M. Elbehag⁶³, L. Fabris⁶⁴, W. Fairbank⁶⁵, J. Farine^{66,67,68}, Y. S. Fu⁶⁹, D. Gallacher⁷⁰, P. Gauran⁷¹, G. Giacomini⁷², C. Gingras⁷³, D. Goddard⁷⁴, R. Gomez⁷⁵, G. Gratta⁷⁶, C. A. Hardy⁷⁷, S. Hedges⁷⁸, M. Heffner⁷⁹, E. Hein⁸⁰, J. Holt⁸¹, E. W. Hoppe⁸², J. Hoff⁸³, A. House⁸⁴, W. Hunt⁸⁵, A. Iverson⁸⁶, X. S. Jiang⁸⁷, A. Karvella⁸⁸, L. J. Kaufman⁸⁹, R. Krücken⁹⁰, A. Kuchner⁹¹, K. S. Kumar⁹², A. Larson⁹³, K. G. Leach⁹⁴, B. G. Lemaire⁹⁵, D. S. Leonard⁹⁶, G. Leonard⁹⁷, G. Li⁹⁸, Z. Li⁹⁹, C. Liebard¹⁰⁰, R. Lindsay¹⁰¹, R. McLeish¹⁰², M. Mahdab¹⁰³, S. Majidi¹⁰⁴, C. Mallikarjuna¹⁰⁵, P. Marage¹⁰⁶, P. Martel-Denis¹⁰⁷, L. Martin¹⁰⁸, J. Masbou¹⁰⁹, N. Massaccesi¹¹⁰, R. McMichael¹¹¹, B. Meng¹¹², K. Munn¹¹³, J. Nalivaiko¹¹⁴, C. R. Natsky¹¹⁵, X. E. Nieves¹¹⁶, J. C. Nieves-Molina¹¹⁷, A. O'Hara¹¹⁸, J. L. Orrell¹¹⁹, G. S. Ostry¹²⁰, C. T. Overman¹²¹, S. Pavesi¹²², A. Perna¹²³, A. Piepke¹²⁴, N. Plekhanov¹²⁵, J. R. Poth¹²⁶, V. Radakov¹²⁷, R. Rapin¹²⁸, G. J. Ramon¹²⁹, T. Ruan¹³⁰, H. K. Raviwar¹³¹, K. Raymond¹³², B. M. Reber¹³³, G. Richardson¹³⁴, J. Ringoette¹³⁵, V. Rist¹³⁶, T. Rossignol¹³⁷, J. C. Rowson¹³⁸, L. Rudolph¹³⁹, R. Saldanha¹⁴⁰, S. Sanghvi¹⁴¹, X. Shang¹⁴², E. Spadoni¹⁴³, V. Stokhove¹⁴⁴, X. L. Sun¹⁴⁵, A. Tidd¹⁴⁶, T. Toes¹⁴⁷, S. Trumbull¹⁴⁸, R. H. M. Tzeng¹⁴⁹, O. A. Tyuk¹⁵⁰, E. Vachon¹⁵¹, M. Vidal¹⁵², S. Viel¹⁵³, G. Visser¹⁵⁴, M. Wagner¹⁵⁵, M. Walent¹⁵⁶, K. Wamba¹⁵⁷, Q. Wang¹⁵⁸, W. Wang¹⁵⁹, Y. Wang¹⁶⁰, M. Watts¹⁶¹, W. Wei¹⁶², L. J. Wen¹⁶³, U. Wiebold^{164,165}, S. Wild¹⁶⁶, M. Worcester¹⁶⁷, W. H. Wu¹⁶⁸, X. Wu¹⁶⁹, L. Xia¹⁷⁰, W. Yan¹⁷¹, H. Yang¹⁷², L. Yang¹⁷³, O. Zdobych¹⁷⁴, J. Zhao¹⁷⁵, T. Ziegler¹⁷⁶

¹ TRIUMF, Vancouver, British Columbia V6T 2A3, Canada
² Institute of High Energy Physics, Chinese Academy of Sciences, Beijing 100049, China
³ Brookhaven National Laboratory, Upton, NY 11973, USA
⁴ Department of Physics, Drexel University, Philadelphia, PA 19104, USA
⁵ Physics Department, McGill University, Montréal, Québec H3A 2T8, Canada
⁶ Amherst Center for Fundamental Interactions and Physics Department, University of Massachusetts, Amherst, MA 01003, USA
⁷ Wright Laboratory, Department of Physics, Yale University, New Haven, CT 06511, USA
⁸ Department of Physics, University of California San Diego, La Jolla, CA 92093, USA
⁹ Physics Department, Stanford University, Stanford, California 94305, USA
¹⁰ Pacific Northwest National Laboratory, Richland, WA 99352, USA
¹¹ Université de Sherbrooke, Sherbrooke, Québec J1K 2R1, Canada
¹² Department of Physics, Carleton University, Ottawa, Ontario K1S 5B6, Canada
¹³ National Research Center "Kurchatov Institute", Moscow 117218, Russia
¹⁴ Lawrence Livermore National Laboratory, Livermore, CA 94550, USA
¹⁵ Department of Physics and Astronomy, University of Kentucky, Lexington, KY 40506
¹⁶ SLAC National Accelerator Laboratory, Menlo Park, CA 94025, USA
¹⁷ Department of Physics, Applied Physics and Astronomy, Rensselaer Polytechnic Institute, Troy, NY 12180, USA
¹⁸ School of Natural Sciences, Laurentian University, Sudbury, Ontario P3E 2C6, Canada
¹⁹ SNO AB, Sudbury, ON P3E 2C6, Canada
²⁰ Institute of Microelectronics, Chinese Academy of Sciences, Beijing 100029, China
²¹ Department of Physics and Astronomy, University of Alabama, Tuscaloosa, AL 35487, USA
²² Department of Physics and Physical Oceanography, University of North Carolina at Wilmington, Wilmington, NC 28403, USA
²³ Physics Department, University of Illinois, Urbana-Champaign, IL 61801, USA
²⁴ Oak Ridge National Laboratory, Oak Ridge, TN 37831, USA
²⁵ Physics Department, Colorado State University, Fort Collins, CO 80523, USA
²⁶ Skyline College, Skyline College, San Bruno, CA 94066, USA
²⁷ Erlangen Centre for Astroparticle Physics (ECAP), Friedrich-Alexander University Erlangen-Nürnberg, Erlangen 91058, Germany
²⁸ Department of Physics and Astronomy, University of British Columbia, Vancouver, British Columbia V6T 1Z1, Canada
²⁹ Department of Physics, University of South Dakota, Vermillion, SD 57069, USA
³⁰ Colorado school of mines, Department of Physics, Colorado School of Mines, Golden, CO 80401, USA
³¹ IRS Center for Underground Physics, Daegu 74126, Korea
³² Department of Physics and Astronomy, University of the Western Cape, P/B X17 Bellville 7535, South Africa
³³ SUBATECH, IMT Atlantique, CNRS/IN2P3, Université de Nantes, Nantes 44307, France
³⁴ Department of Physics and CEEM, Indiana University, Bloomington, IN 47405, USA

Received: date / Accepted: date

¹e-mail: giacomini@triumf.ca
²Also with: Physics Department, Princeton University, Princeton, NJ 08544, USA
³Also with: University of Chinese Academy of Sciences, Beijing 100049, China
⁴e-mail: enogf@ihep.ac.cn
⁵Now at: Laboratory for Nuclear Science, Massachusetts Institute of Technology, Cambridge, MA, USA
⁶Permanent at: King Abdulaziz City for Science and Technology, KACST, Riyadh 11442, Saudi Arabia
⁷Now at: Canon Medical Research, USA
⁸Now at: Nuclear Science Division, Lawrence Berkeley National Laboratory, USA